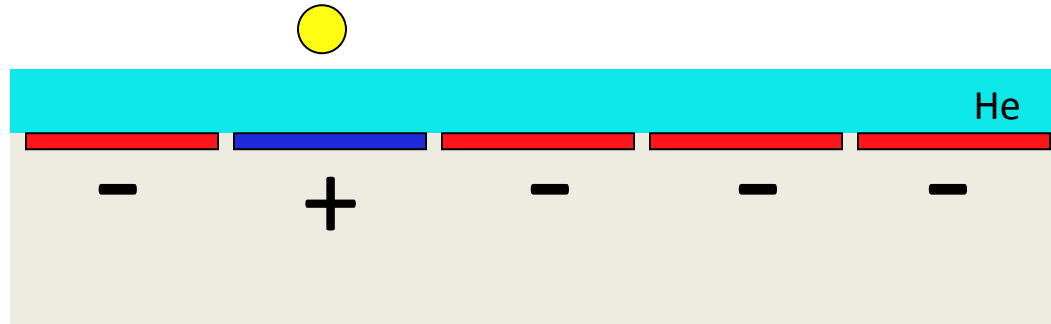


# (Extremely efficient) clocked electron transport on superfluid helium



Maika Takita, Forrest Bradbury<sup>1</sup>, Stephen A Lyon

Department of Electrical Engineering, Princeton University

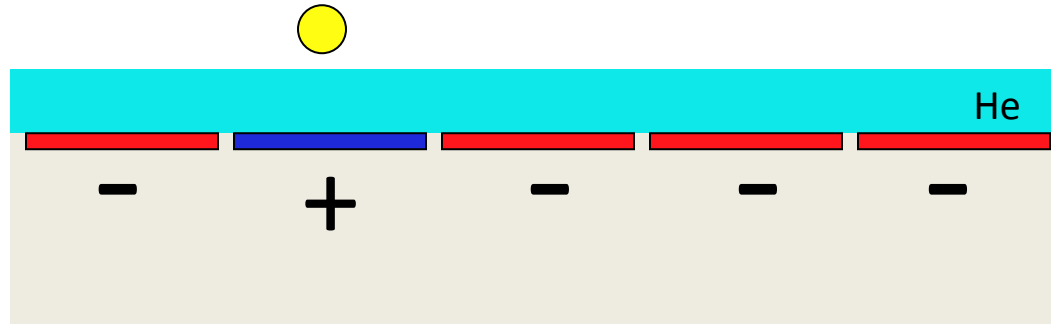
Kevin Eng<sup>2</sup>, Tom M Gurrieri, Kathy J Wilkel, Malcom S Carroll

Sandia National Laboratories

1. Present address: Amsterdam University College, Amsterdam, The Netherlands
2. Present address: HRL Laboratories, LLC, Malibu, CA, USA



# Extremely efficient clocked electron transport on superfluid helium



## Outline

### 1. Intro

What can we do with mobile electrons?

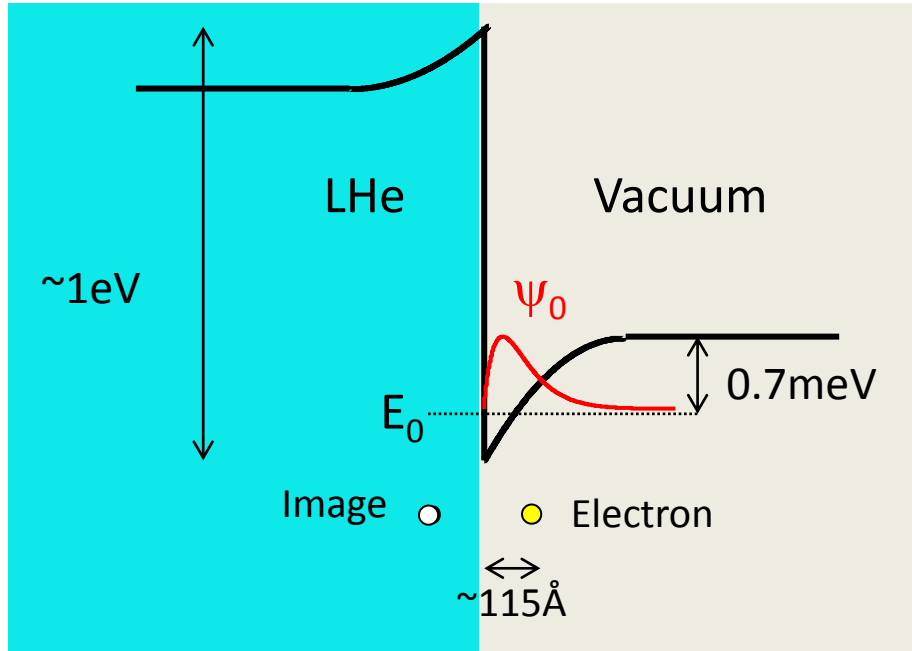
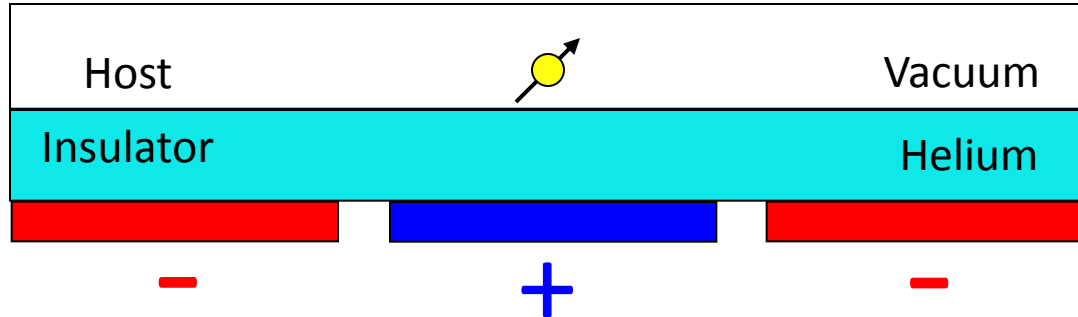
### 2. Sandia Device

Clocking experiment

### 3. IBM Device

What's next?

# Electrons on superfluid helium

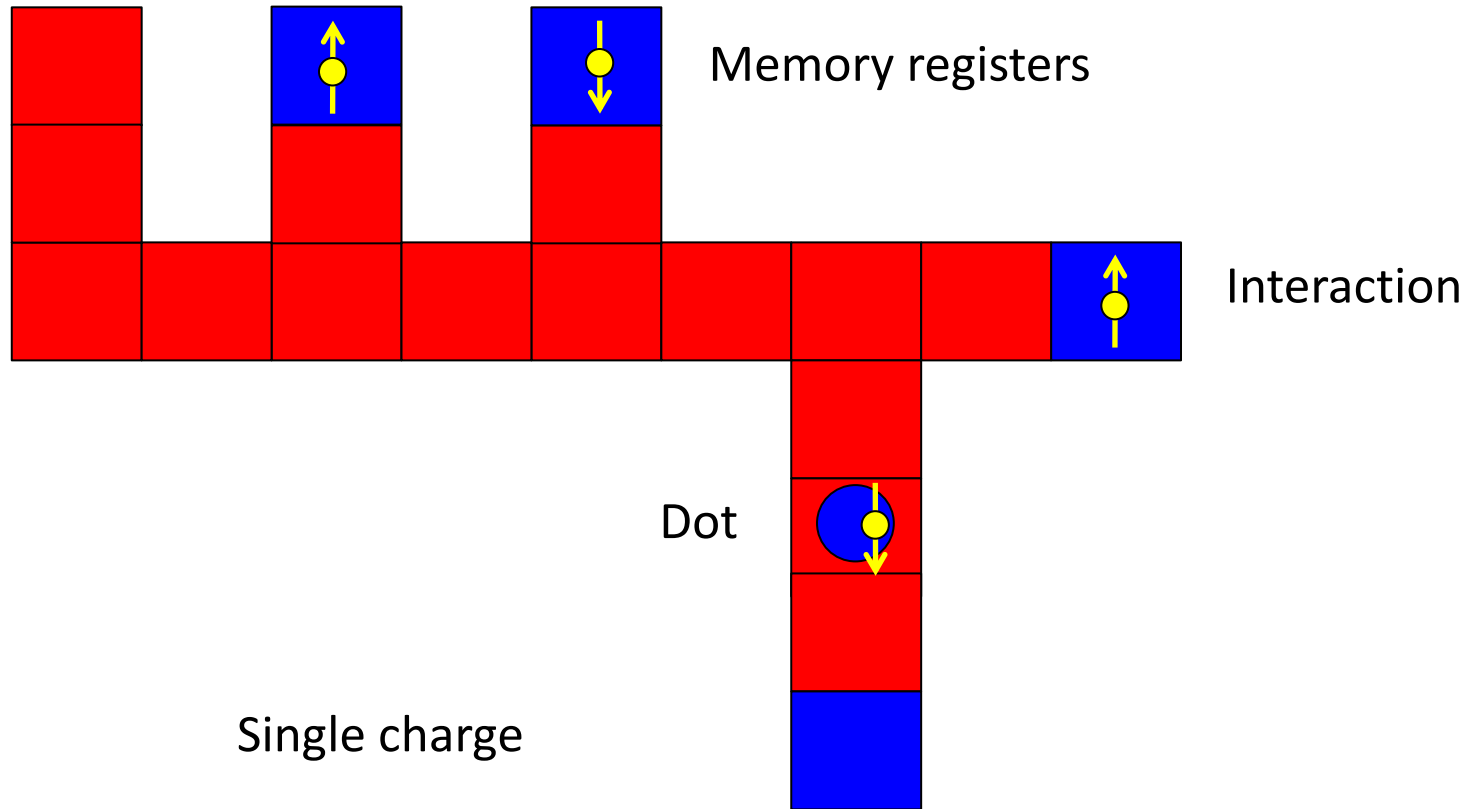


Clean system: Electrons in vacuum

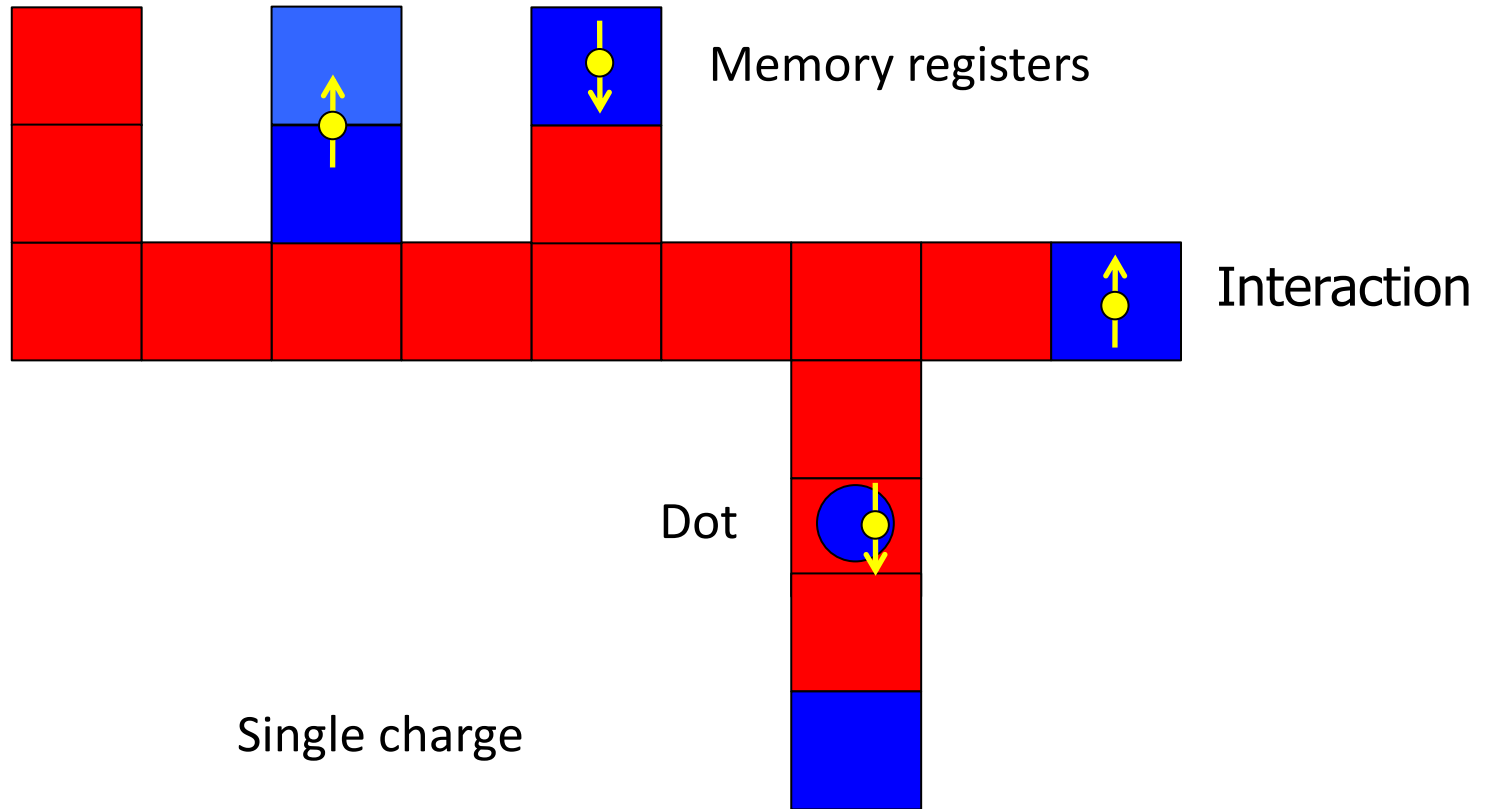
Long spin coherence  
negligible spin-orbit interaction

$\Rightarrow$  Able to move electrons without spin decoherence!

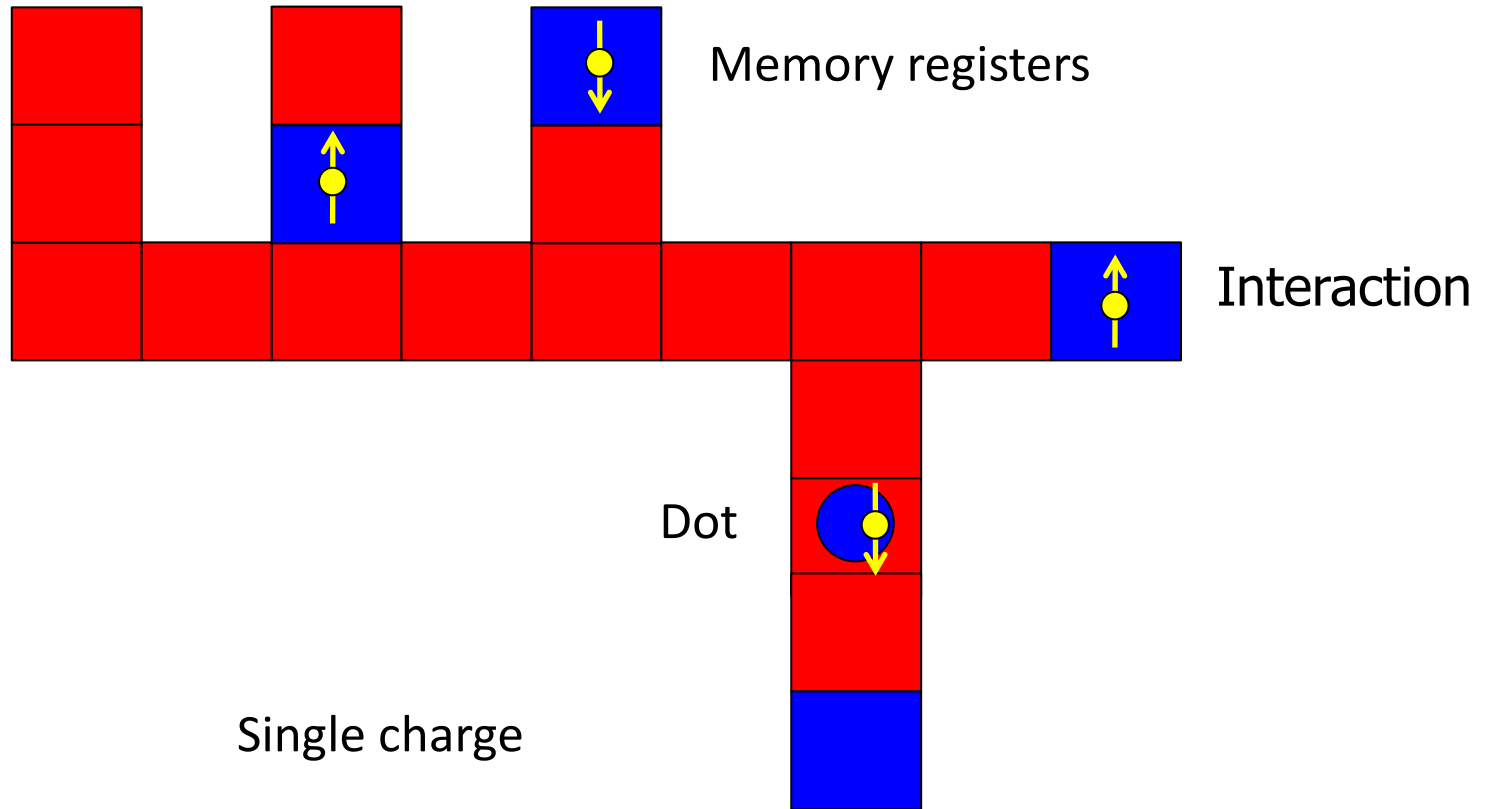
# Transport enabled computation



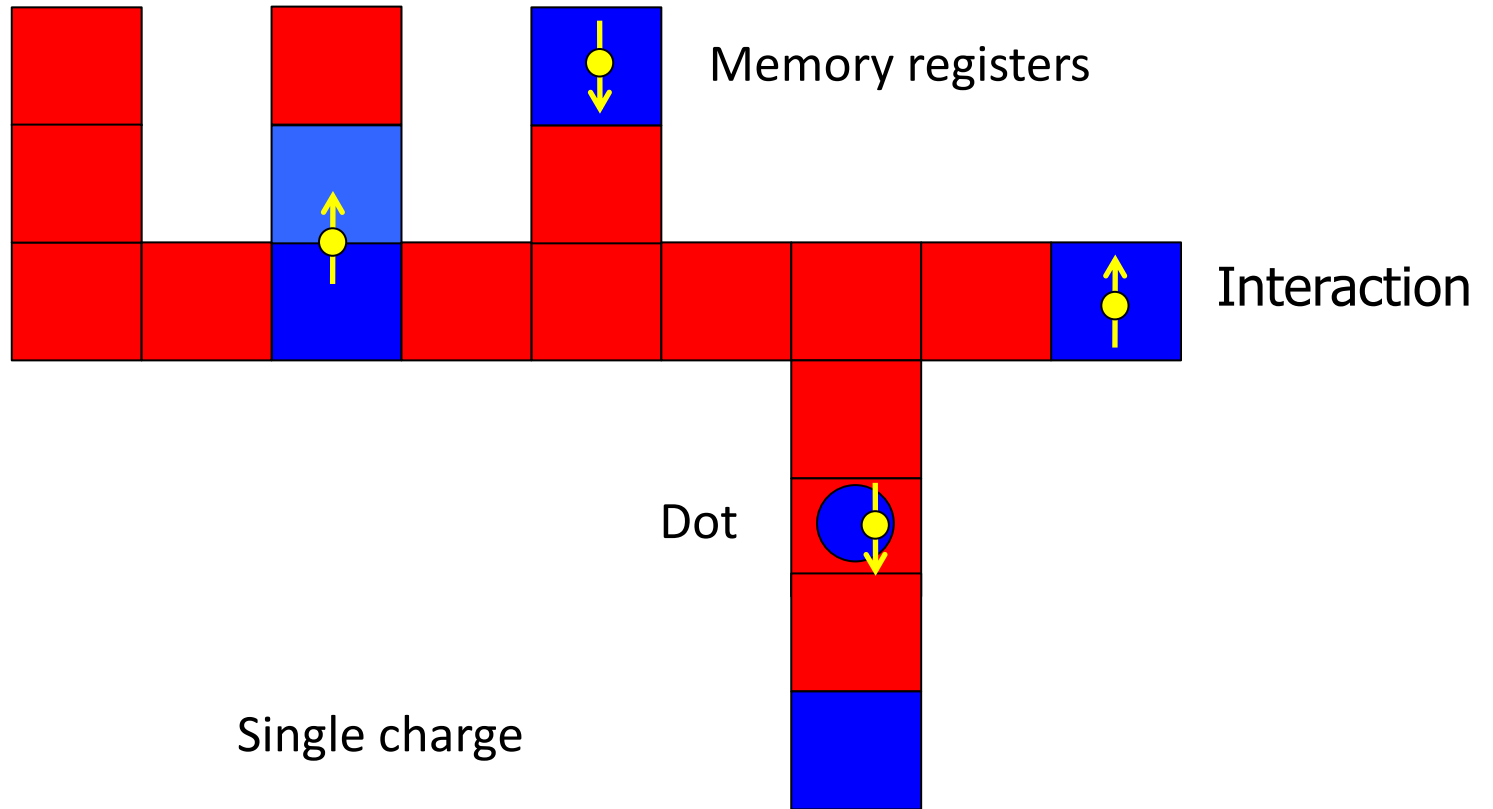
# Transport enabled computation



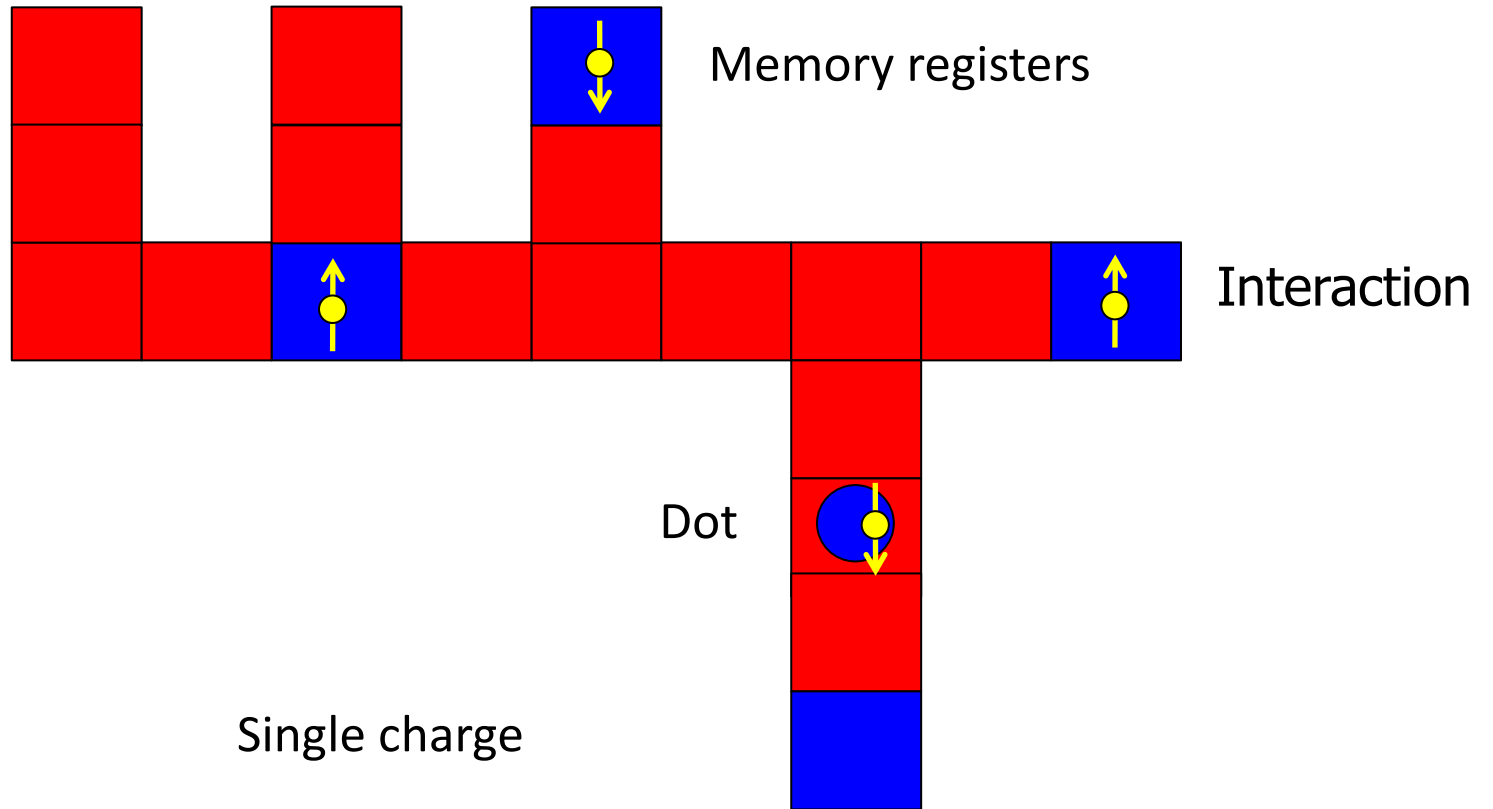
# Transport enabled computation



# Transport enabled computation

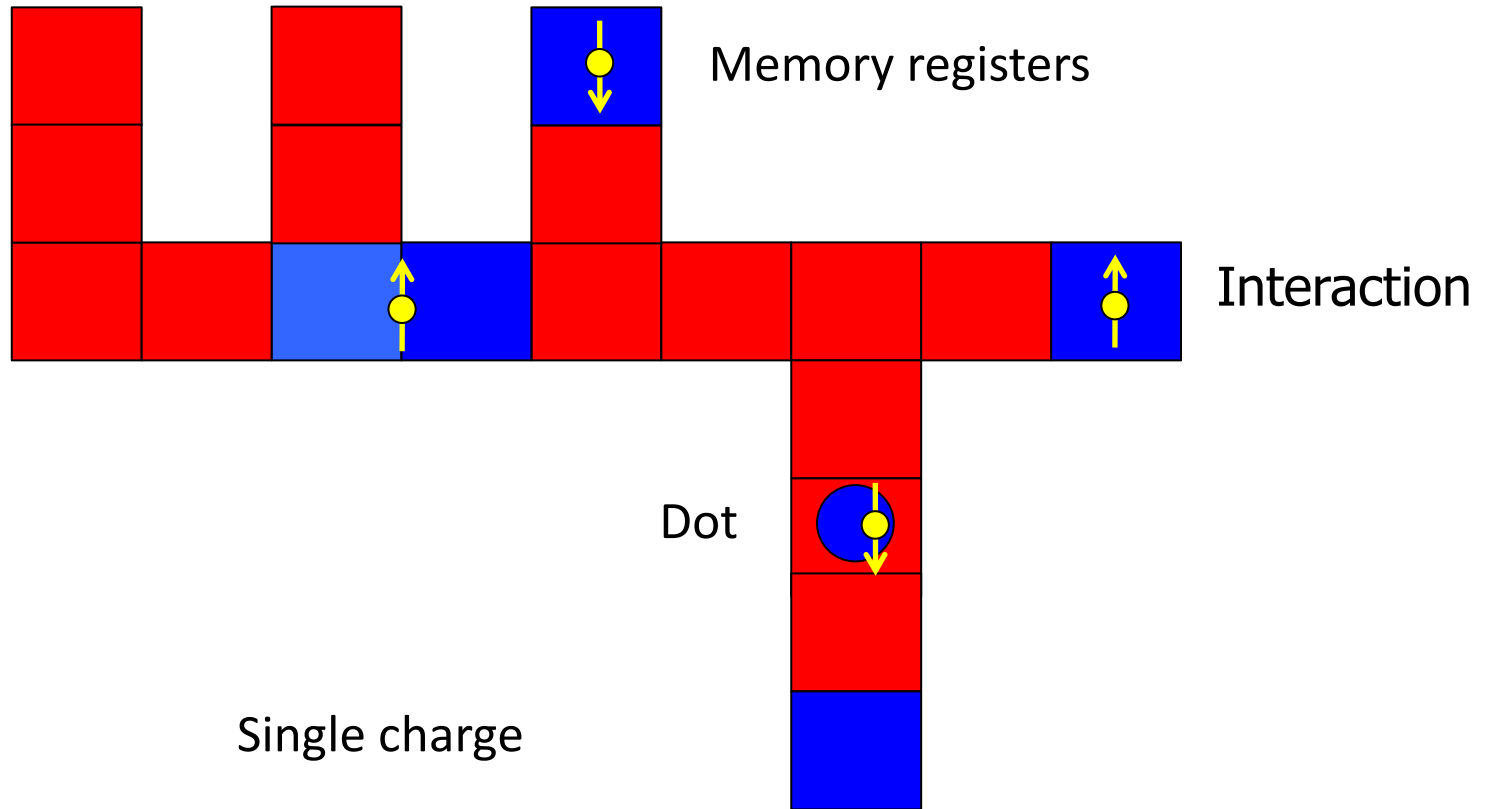


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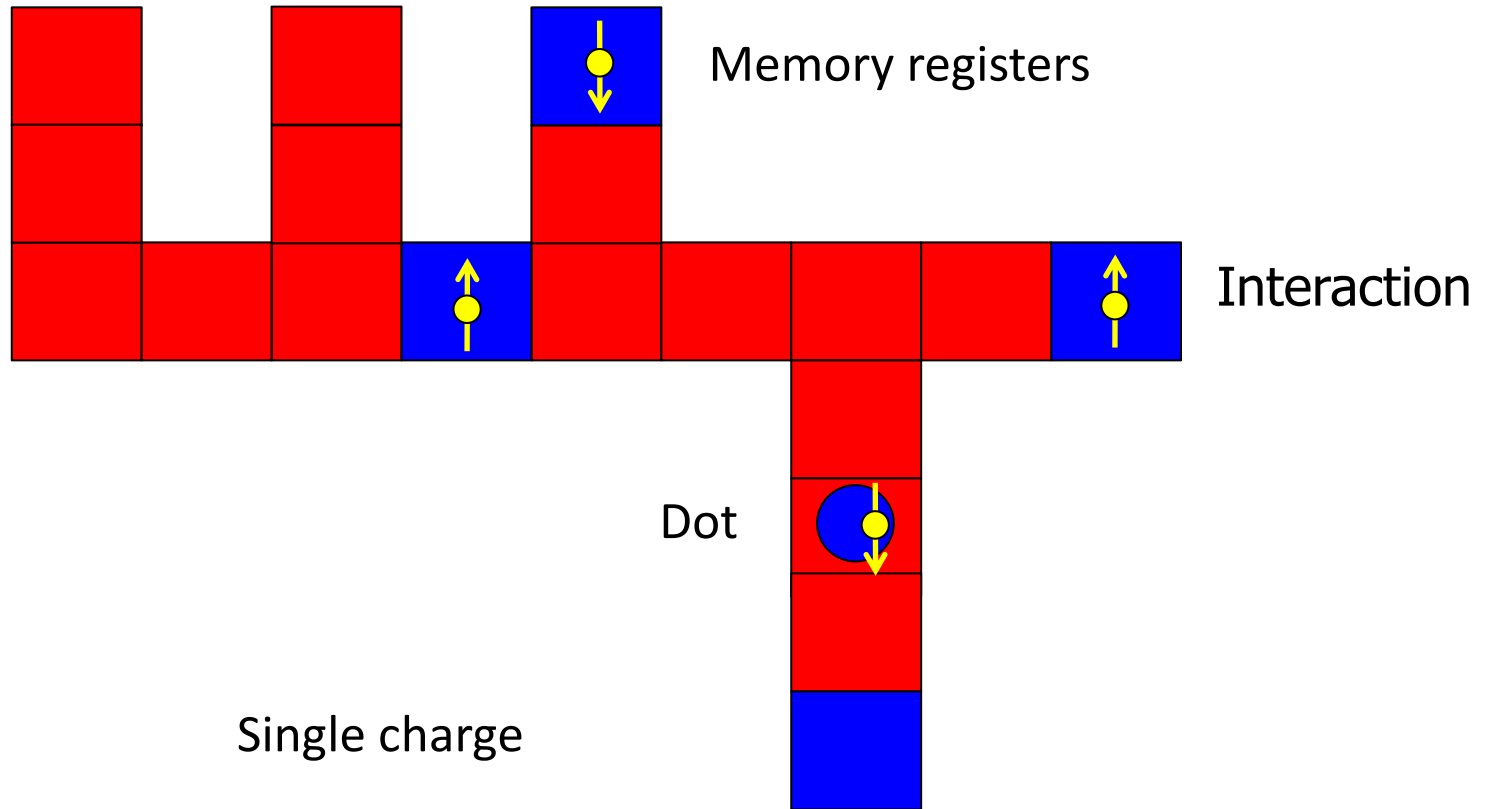




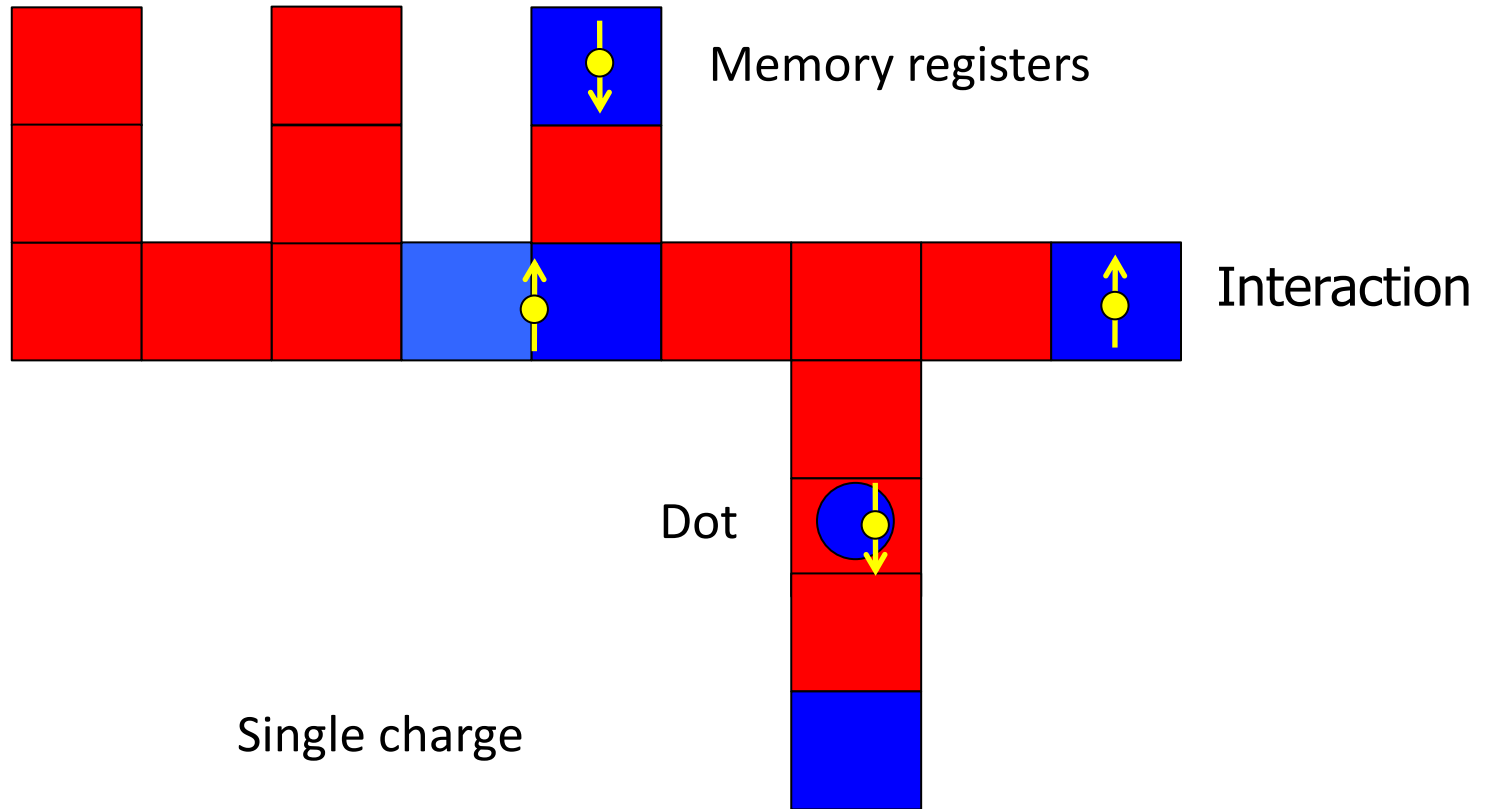
# Transport enabled computation



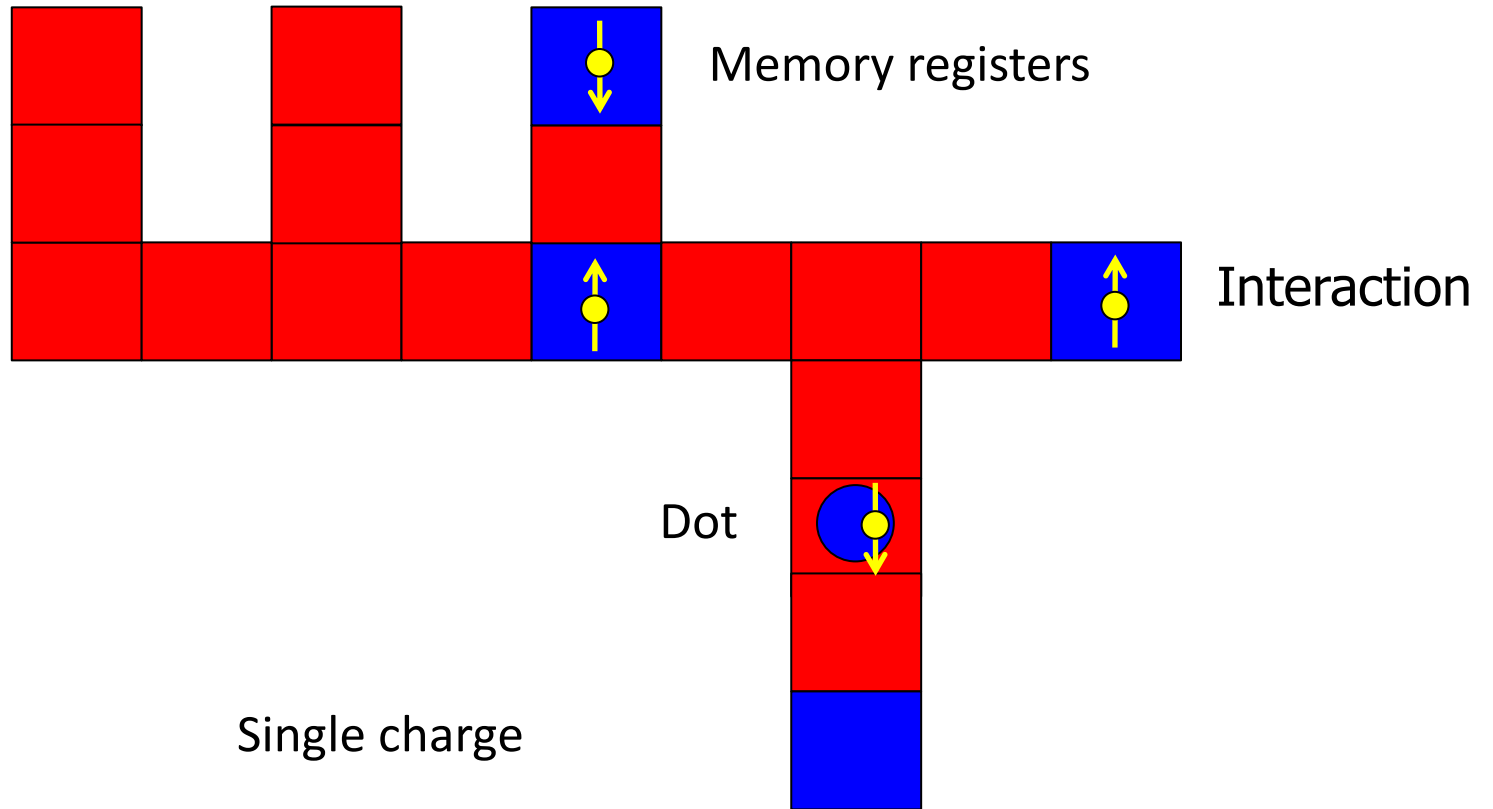
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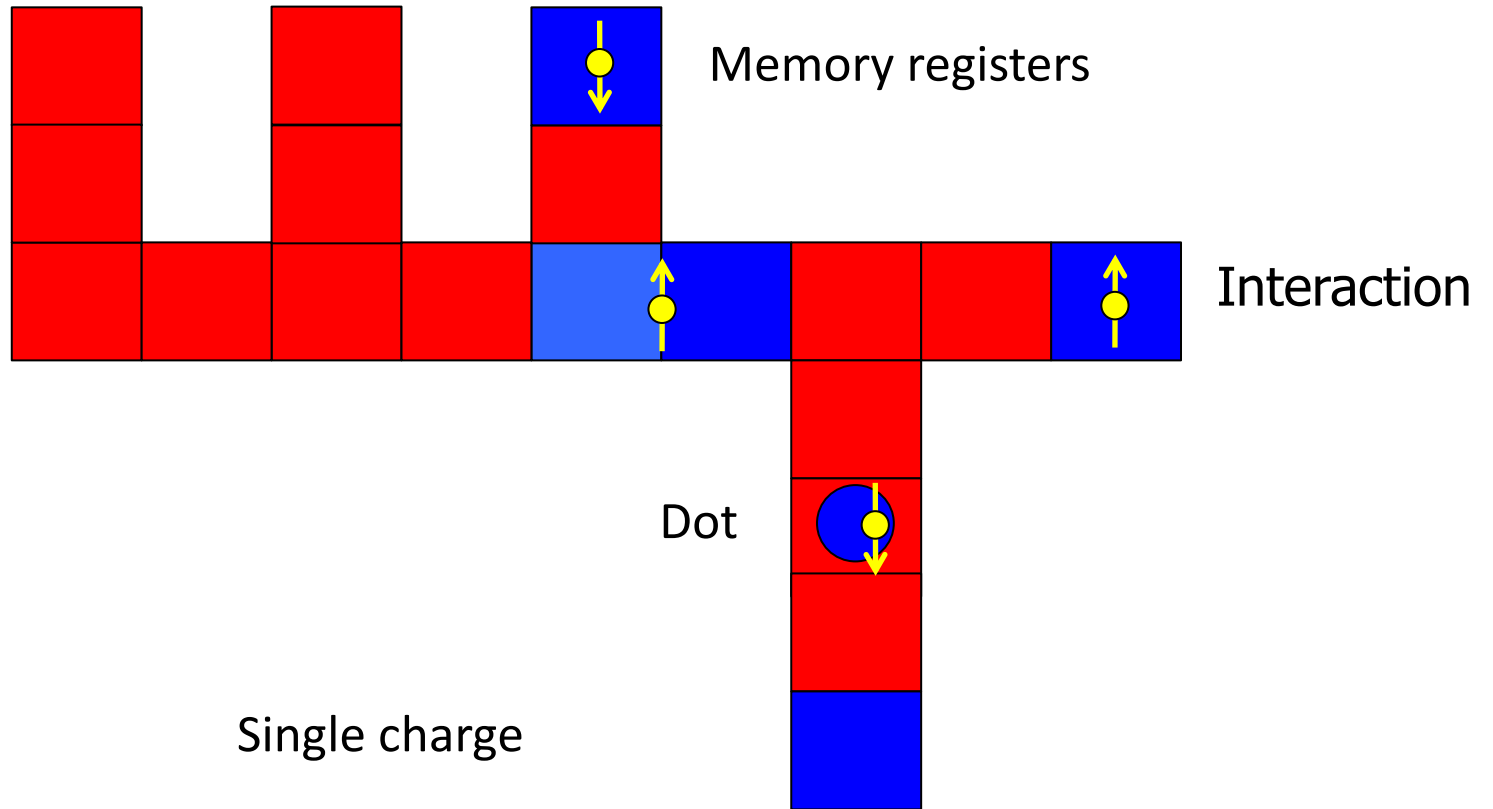
# Transport enabled computation



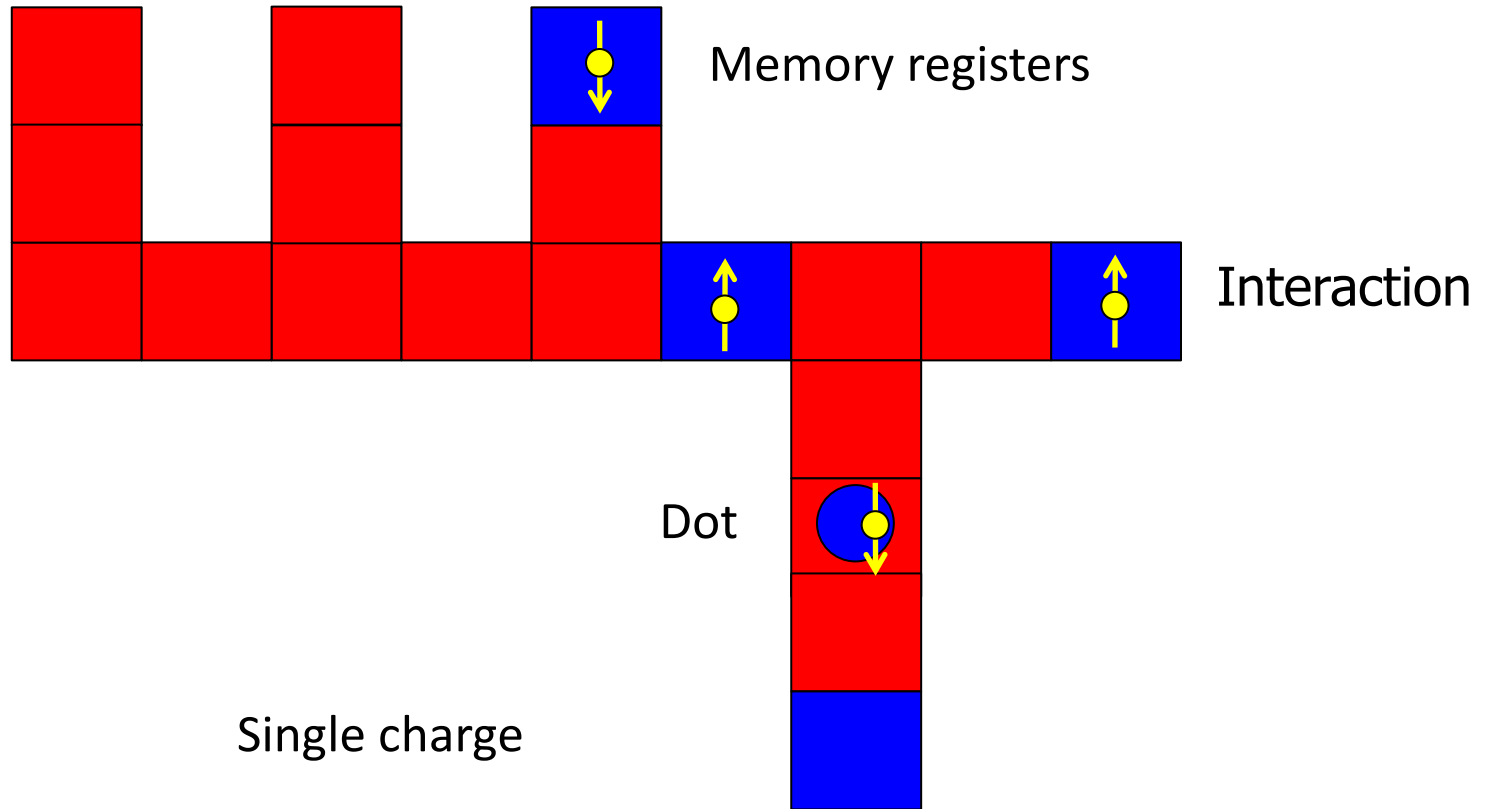
# Transport enabled computation



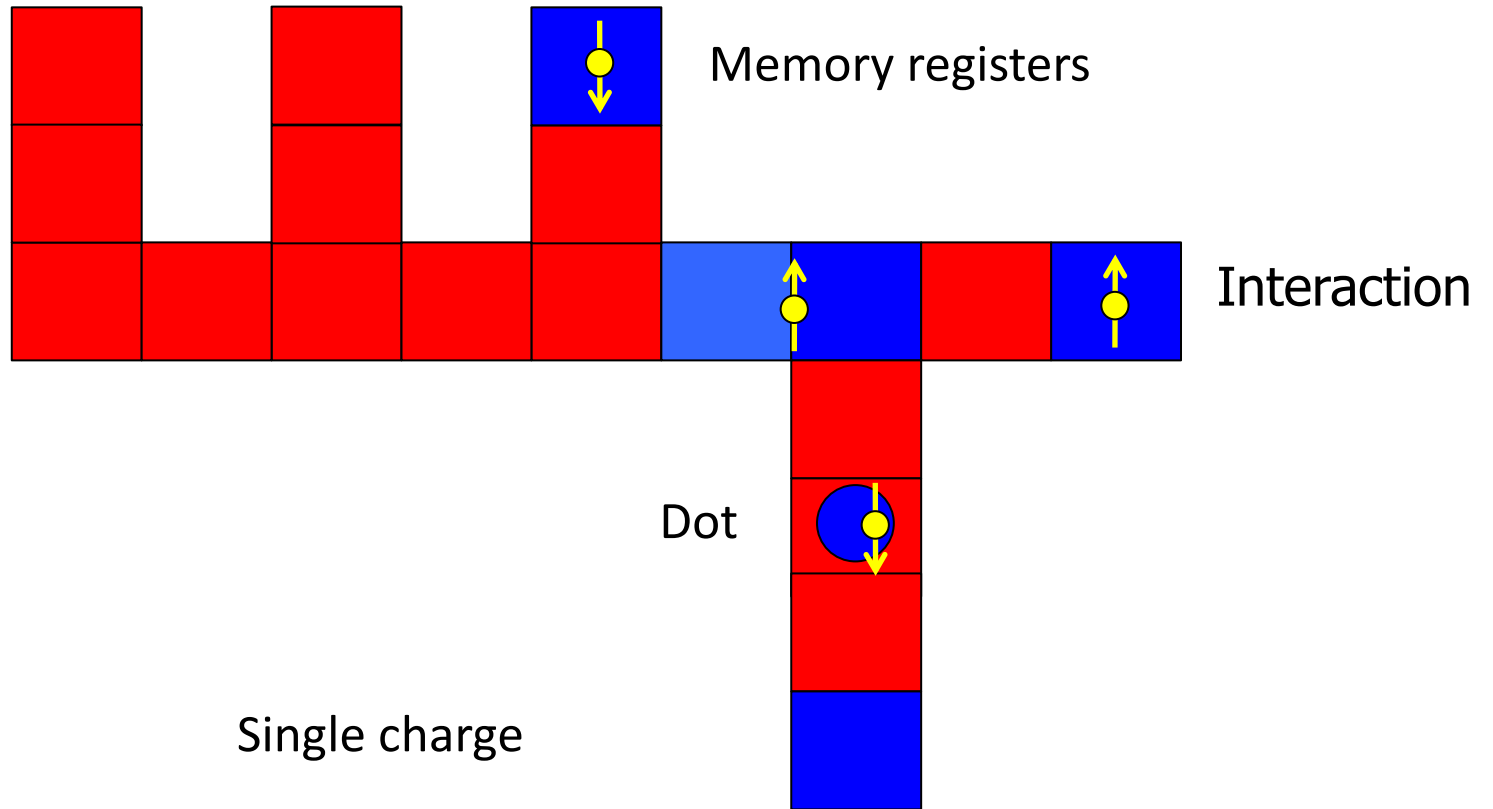
# Transport enabled computation



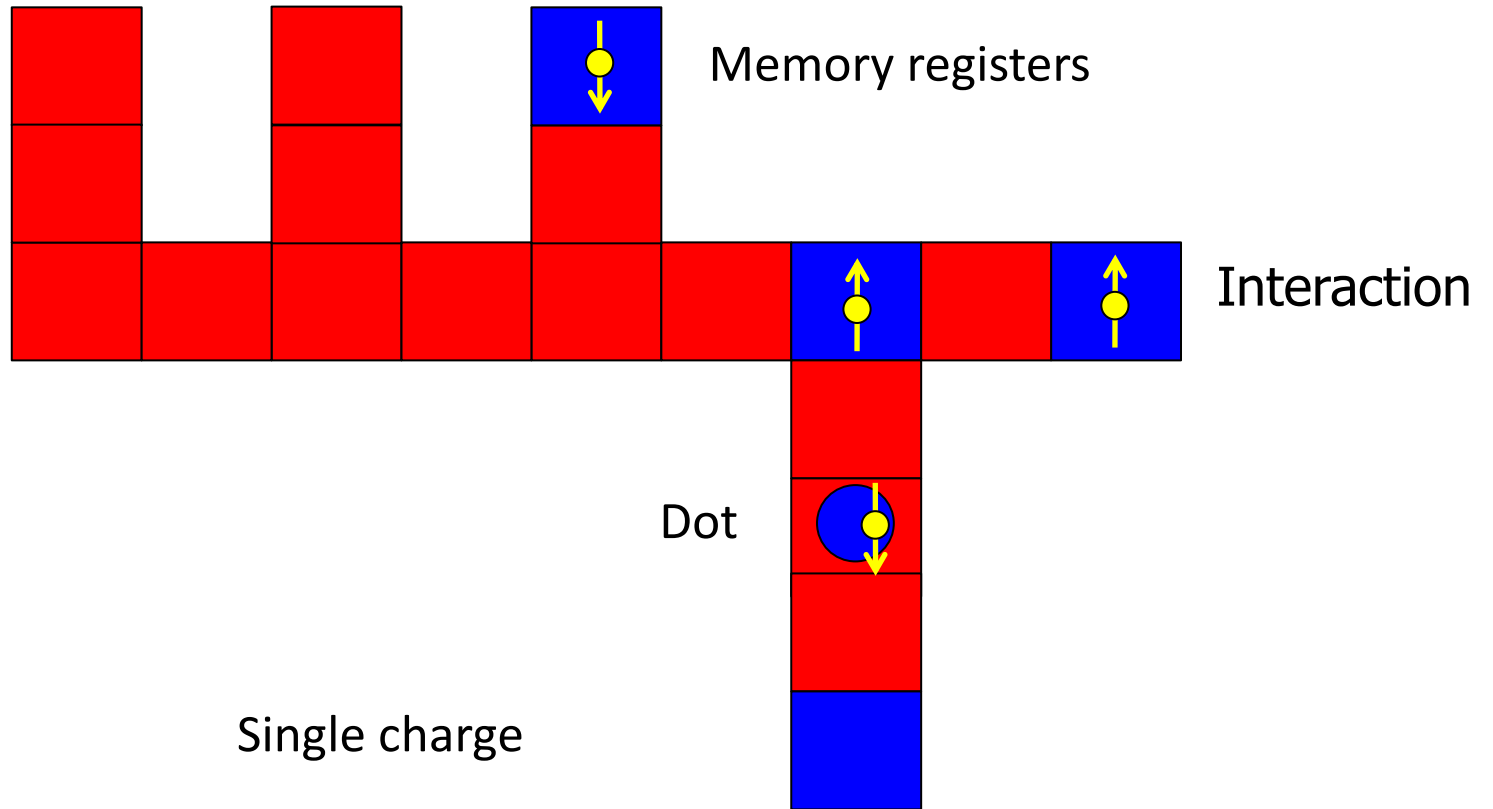
# Transport enabled computation



# Transport enabled computation

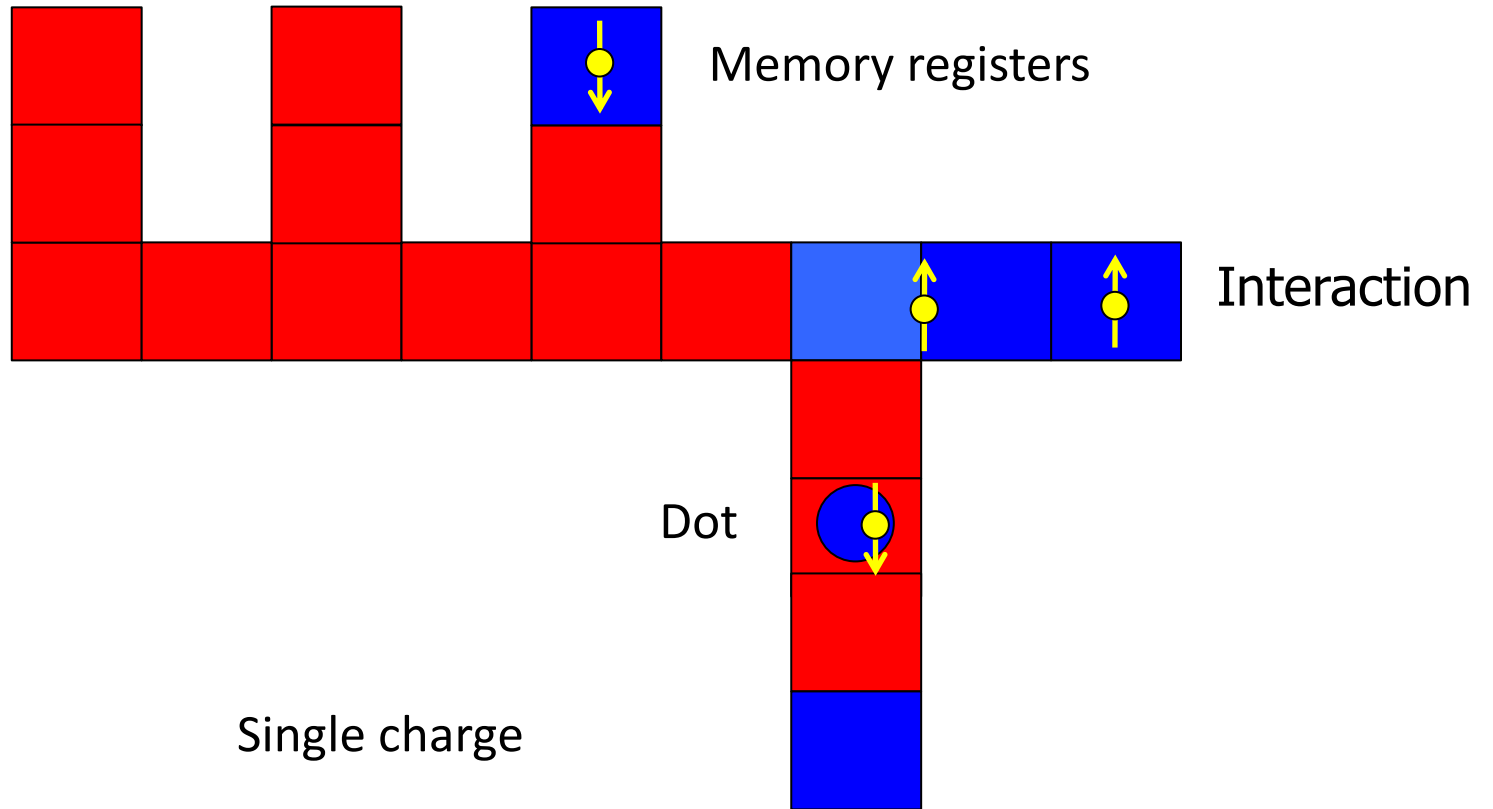


# Transport enabled computation

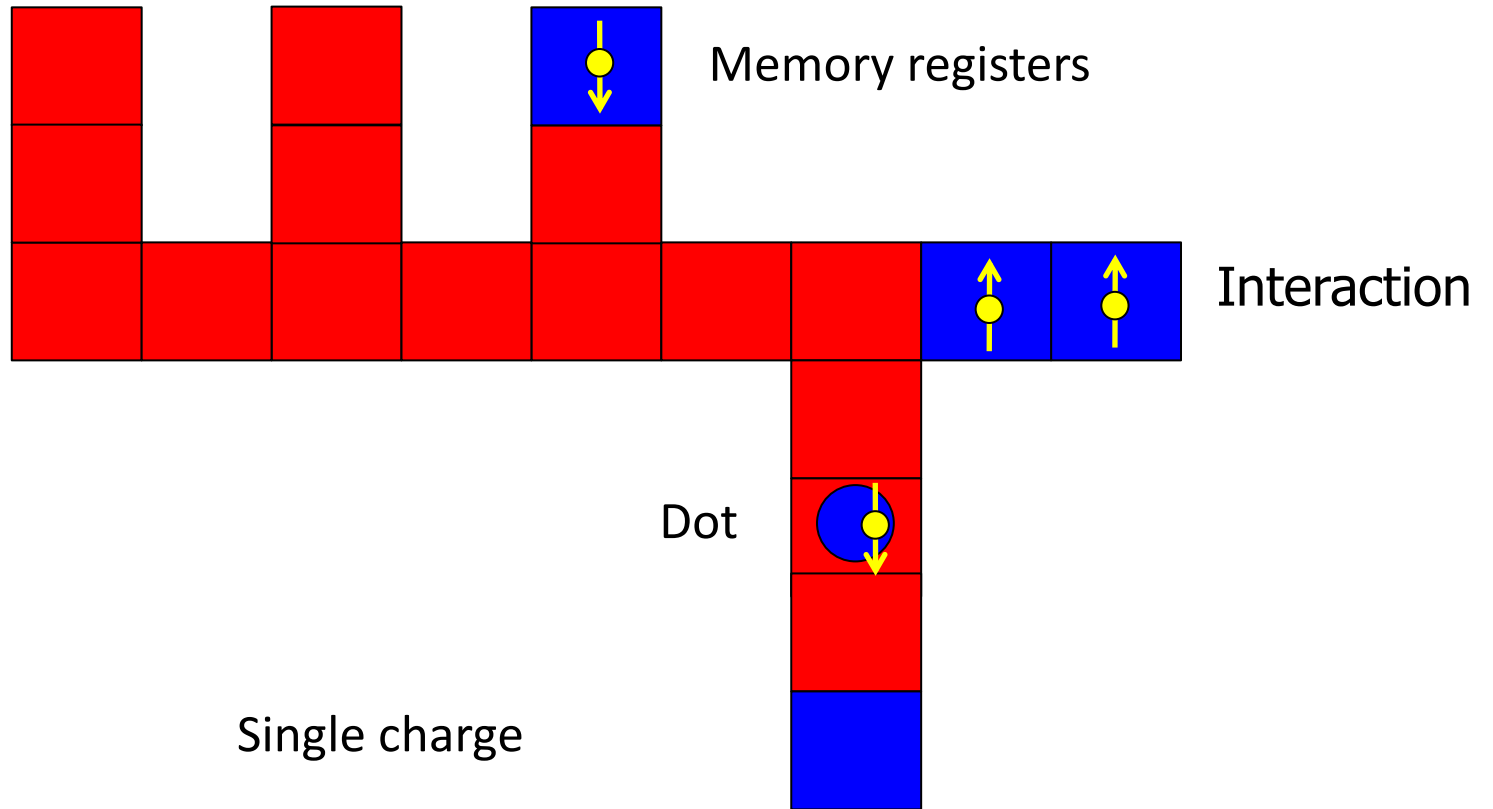




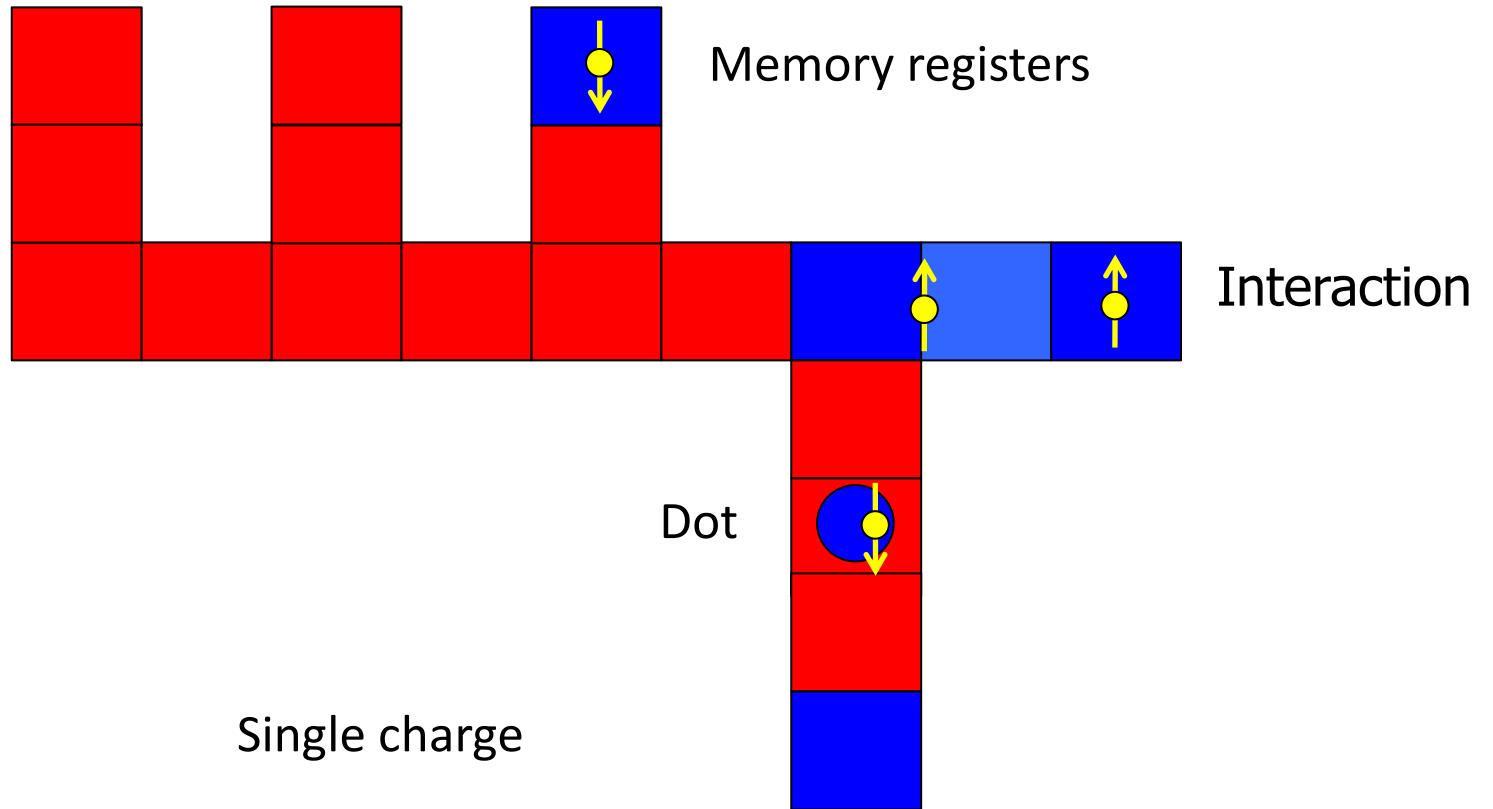
# Transport enabled computation



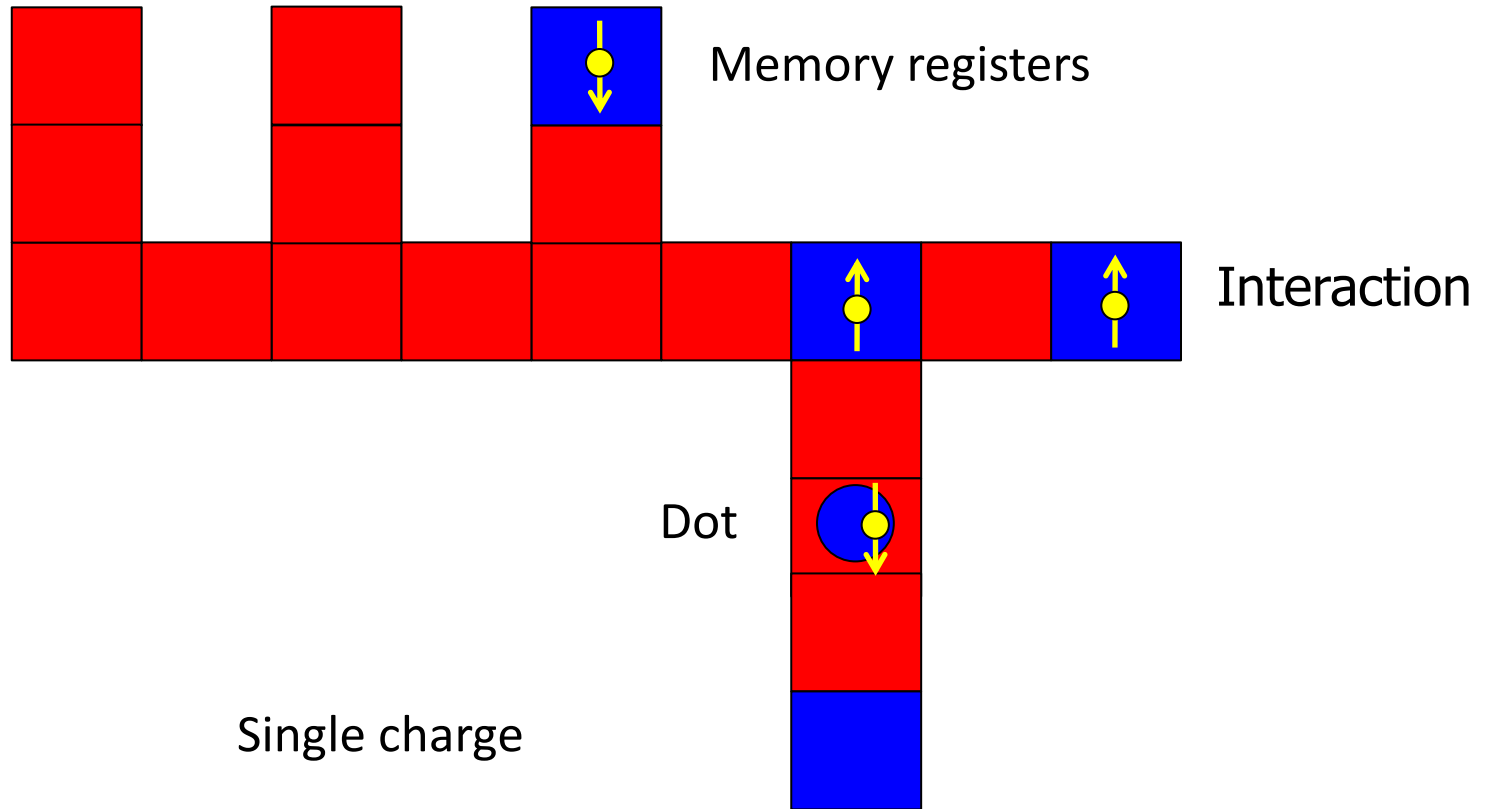
# Transport enabled computation



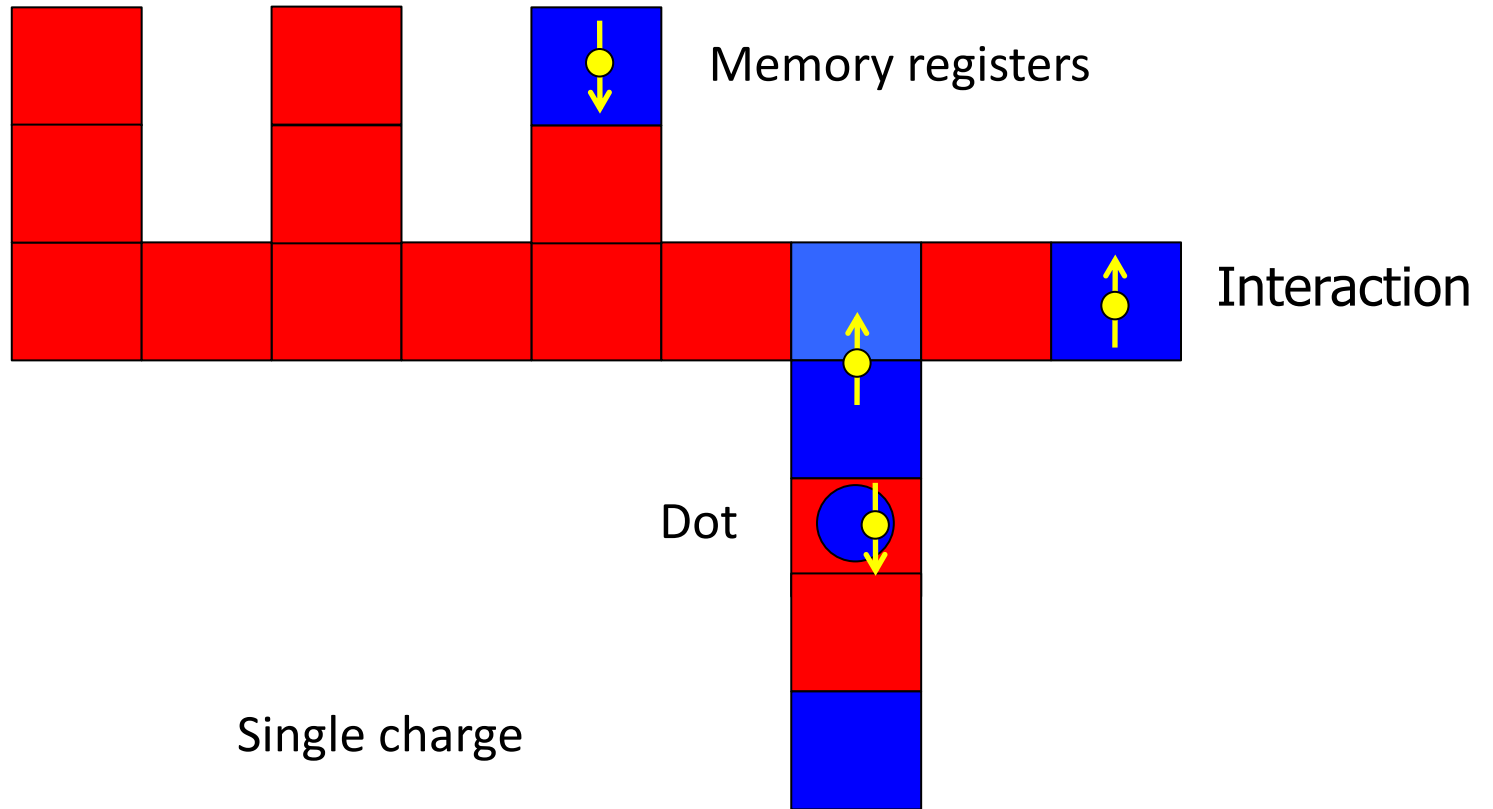
# Transport enabled computation



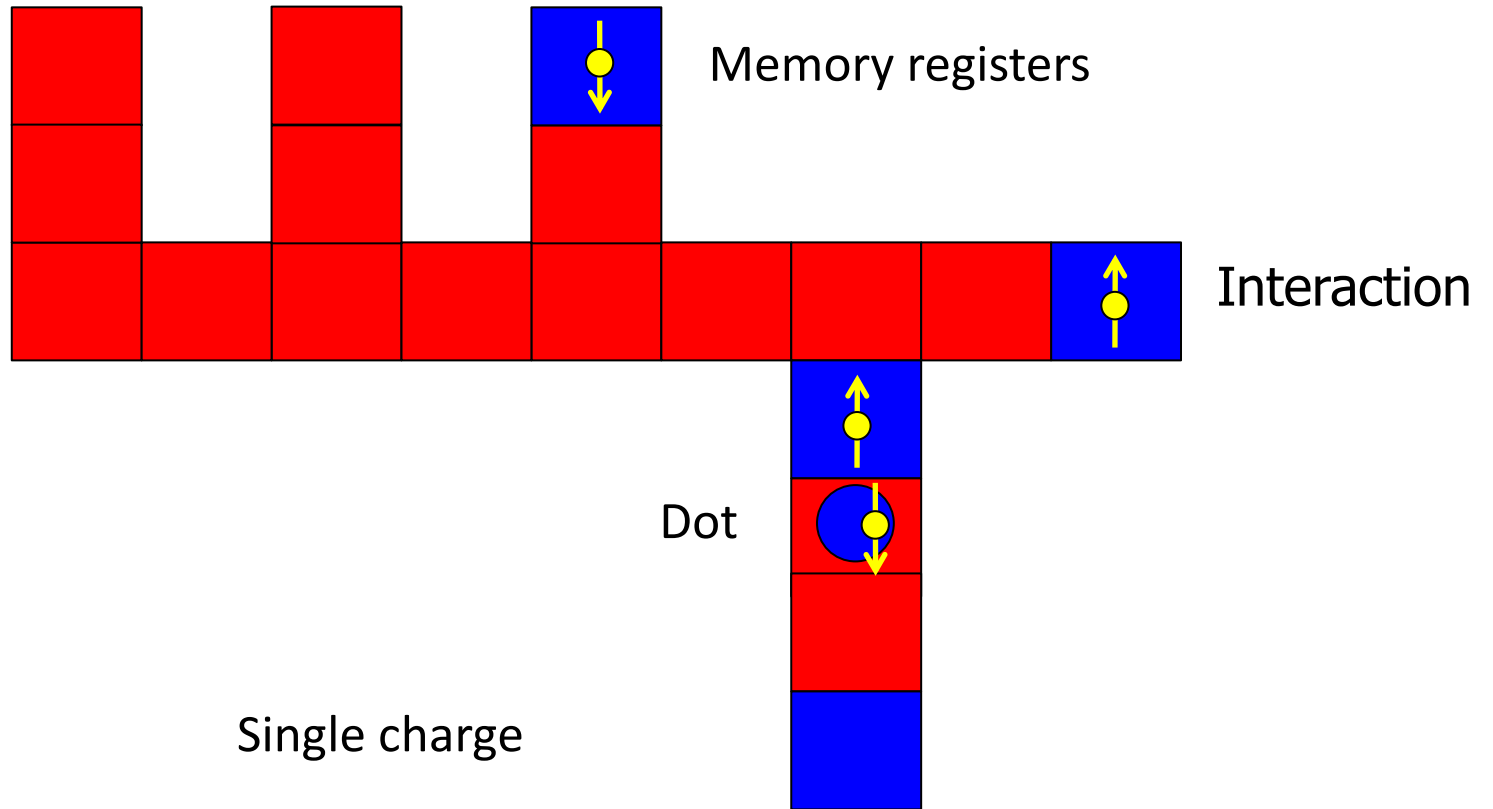
# Transport enabled computation



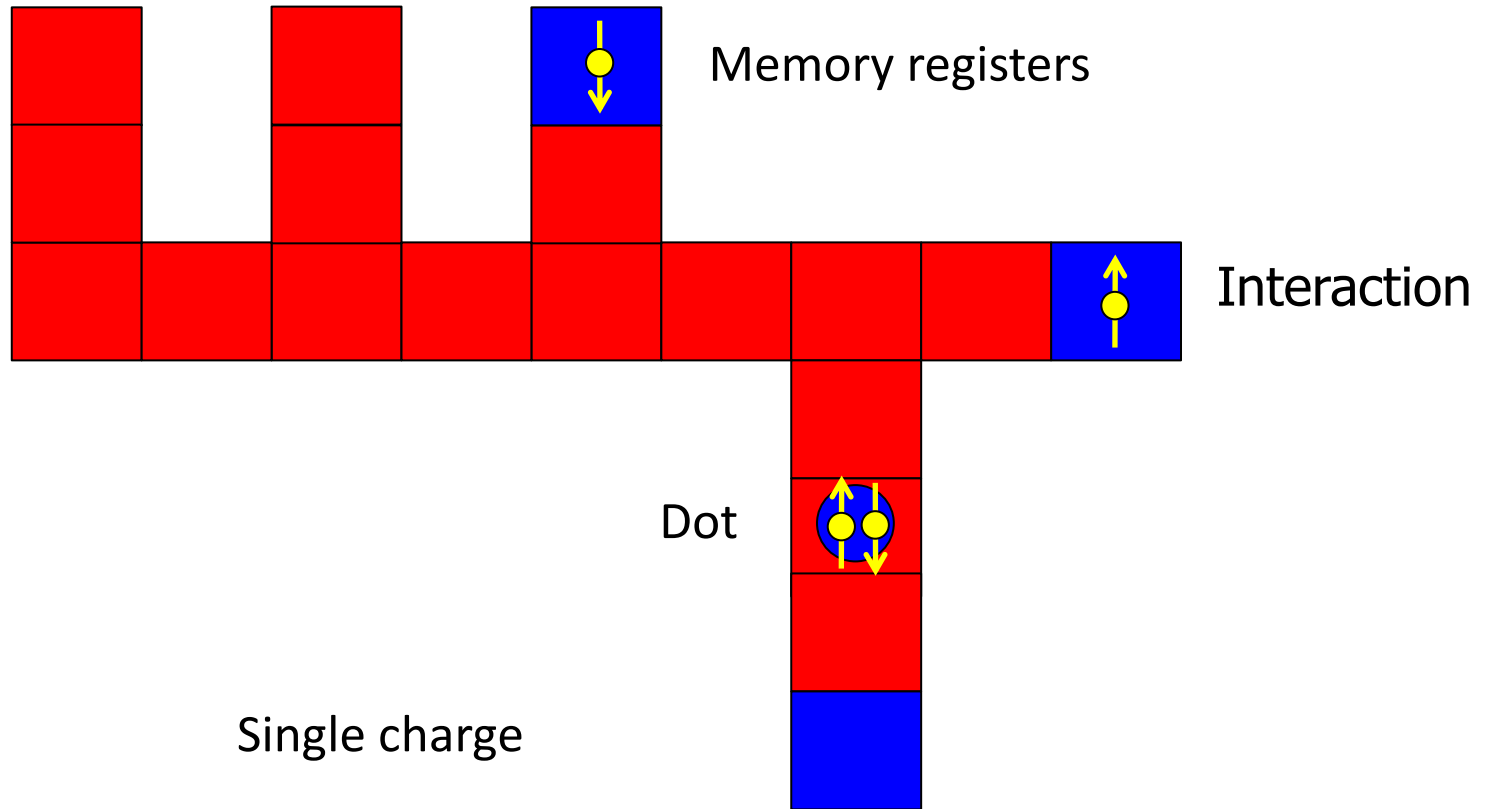
# Transport enabled computation



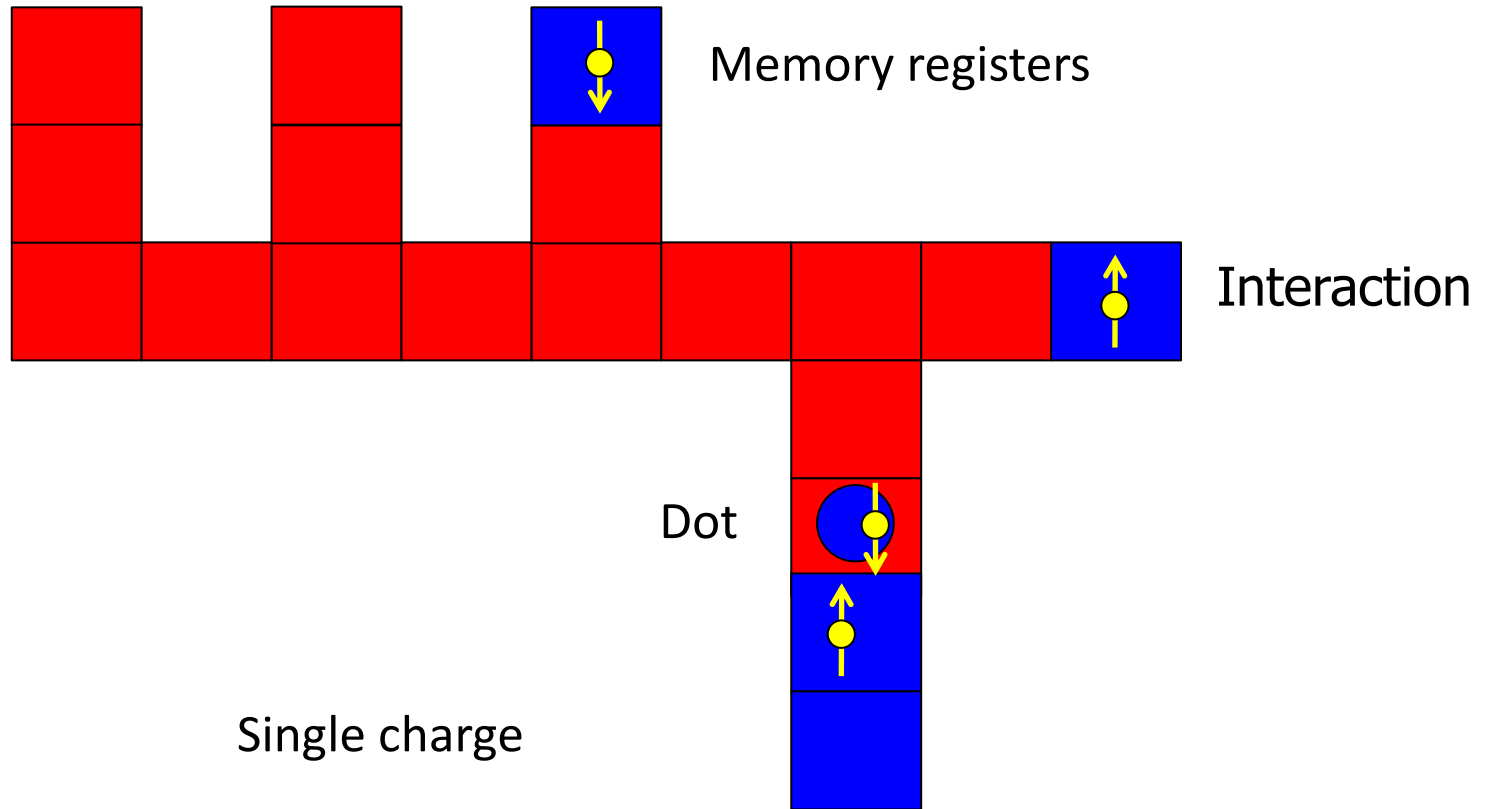
# Transport enabled computation



# Transport enabled computation

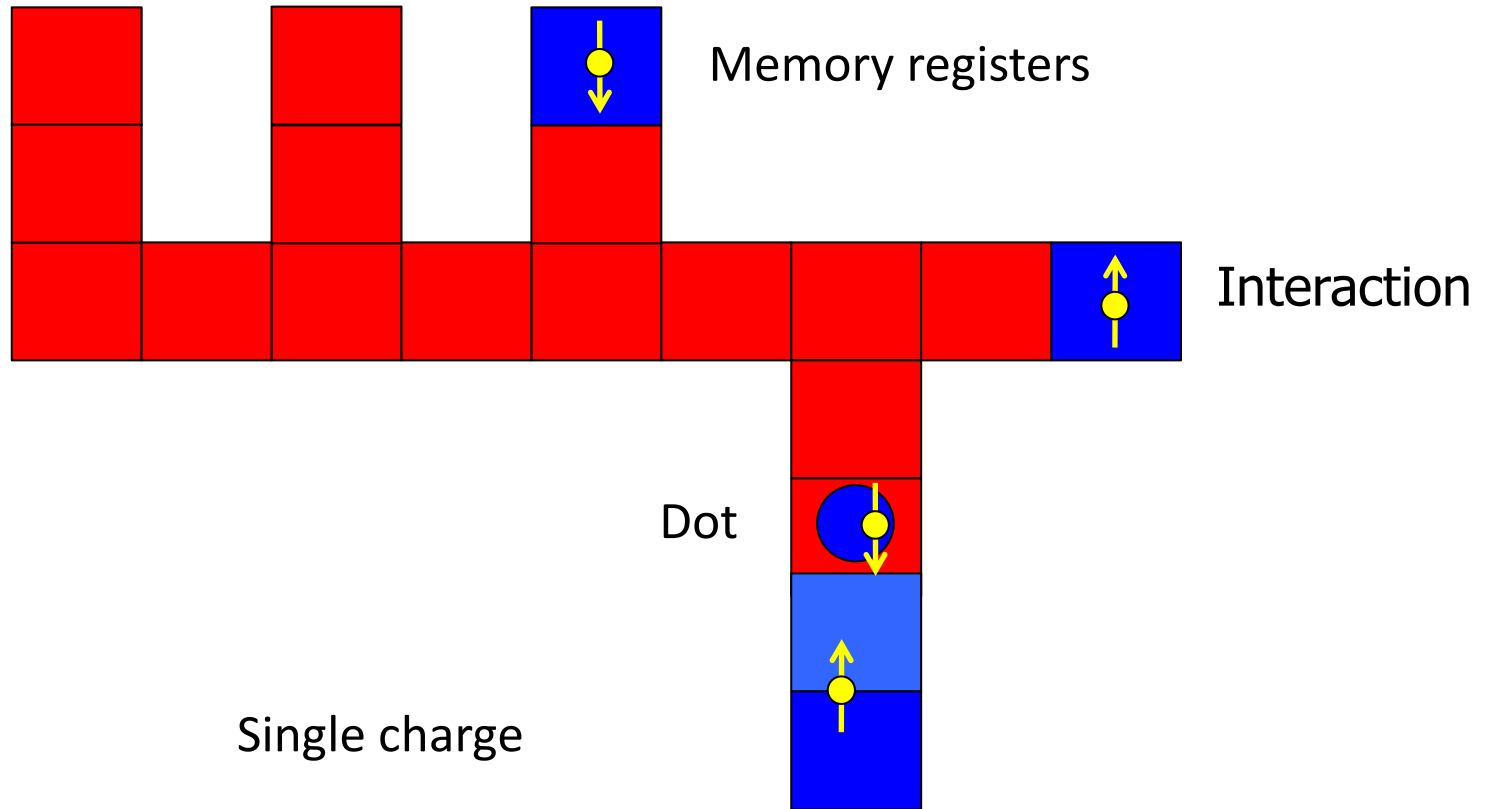


# Transport enabled computation

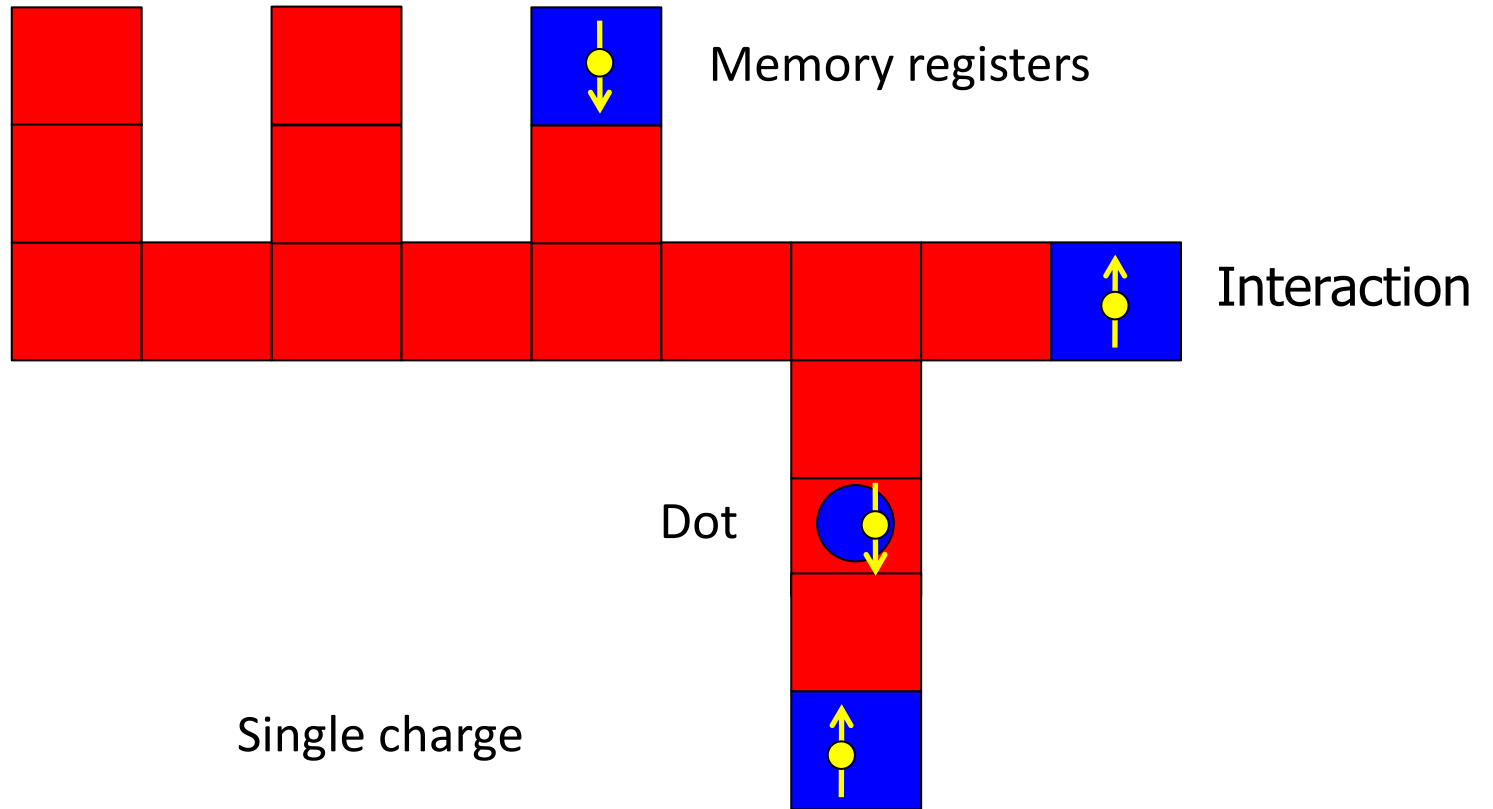




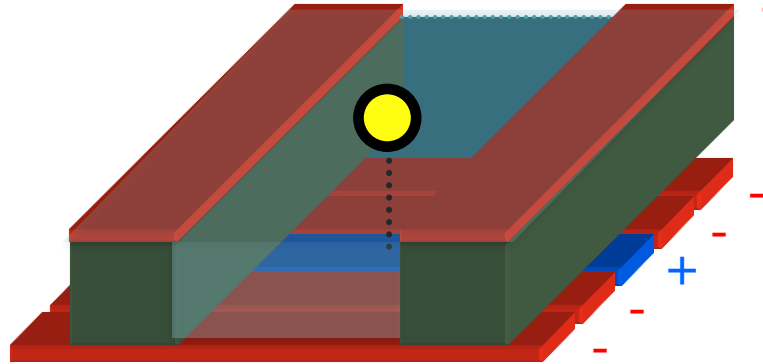
# Transport enabled computation



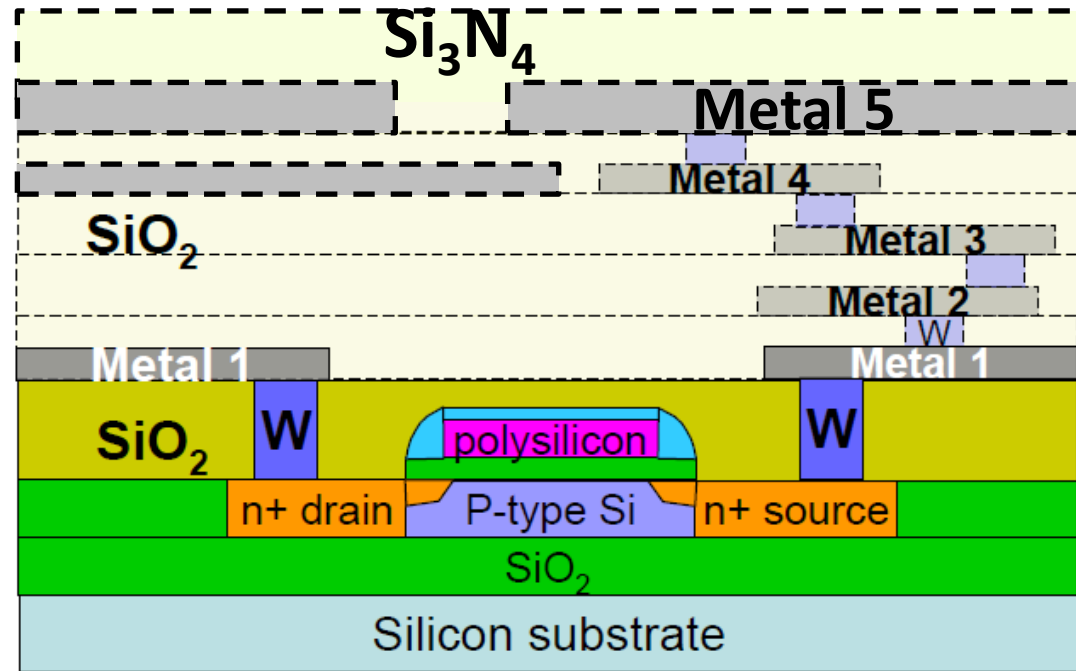
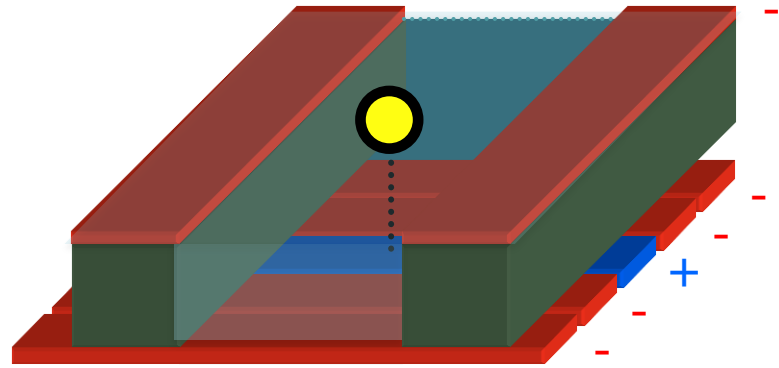
# Transport enabled computation

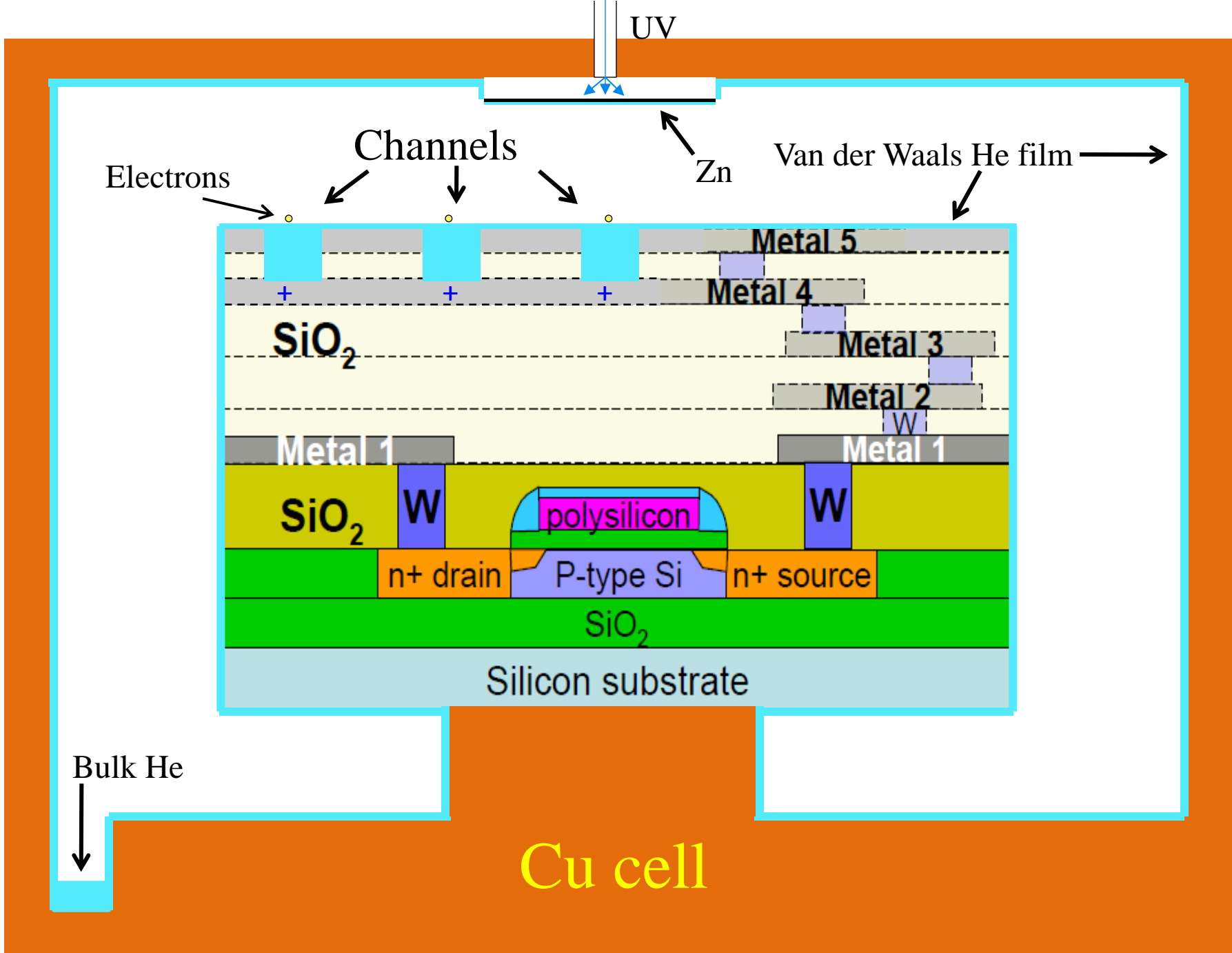


# Channel Device with Sandia CMOS7

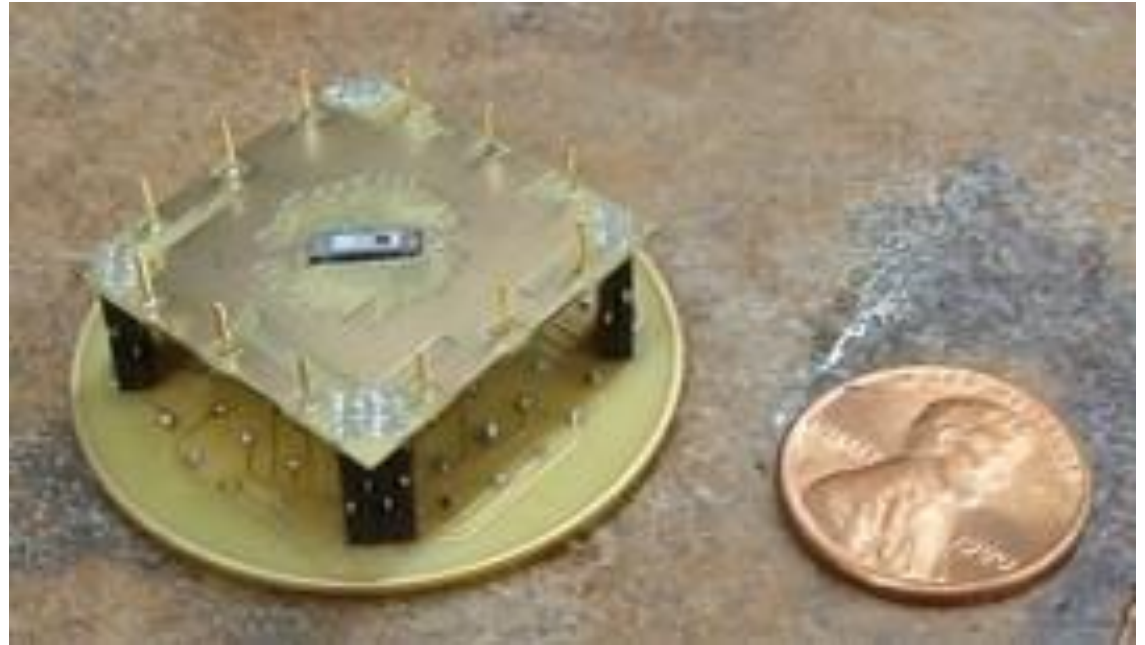


# Channel Device with Sandia CMOS7

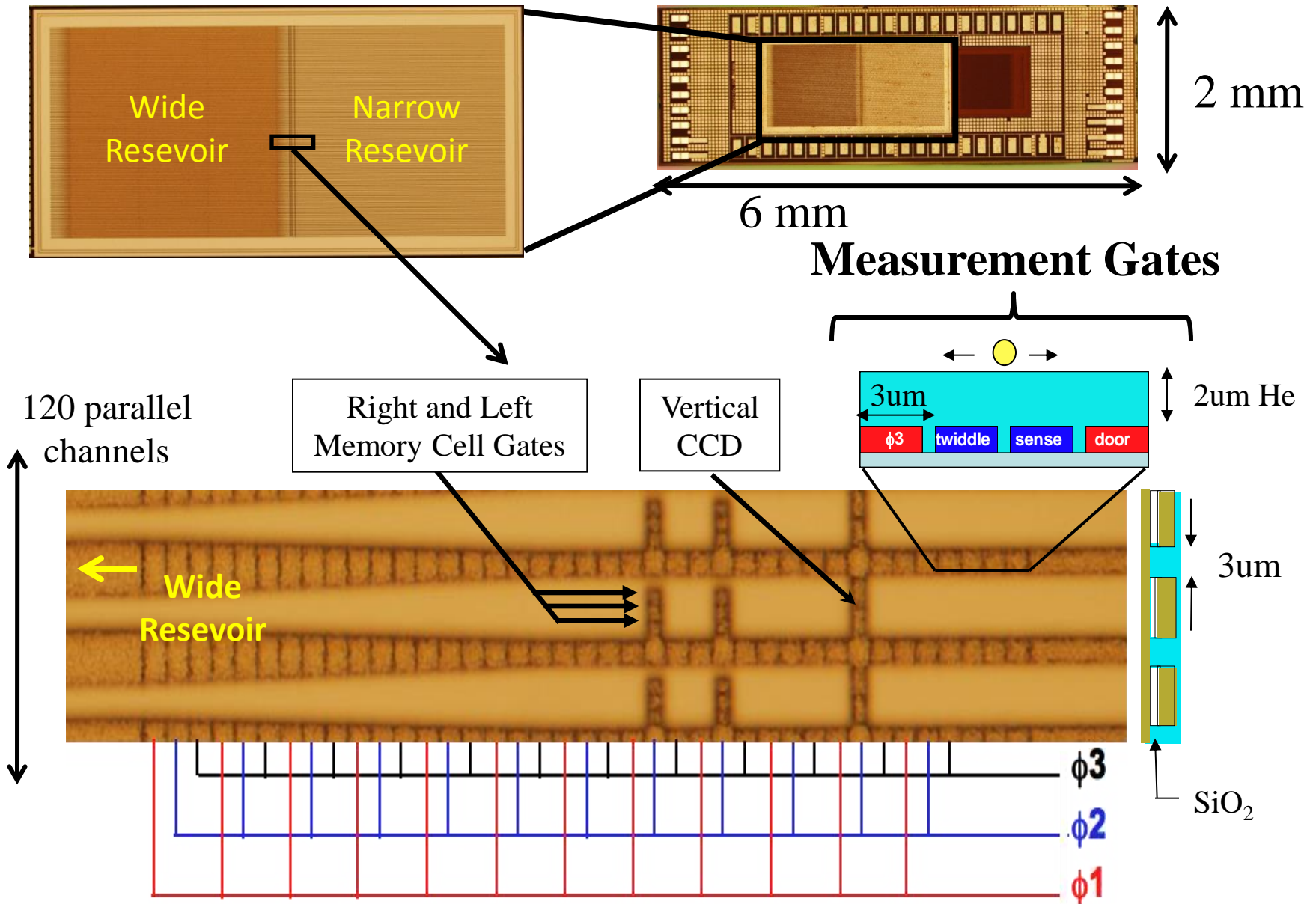




# Experiment



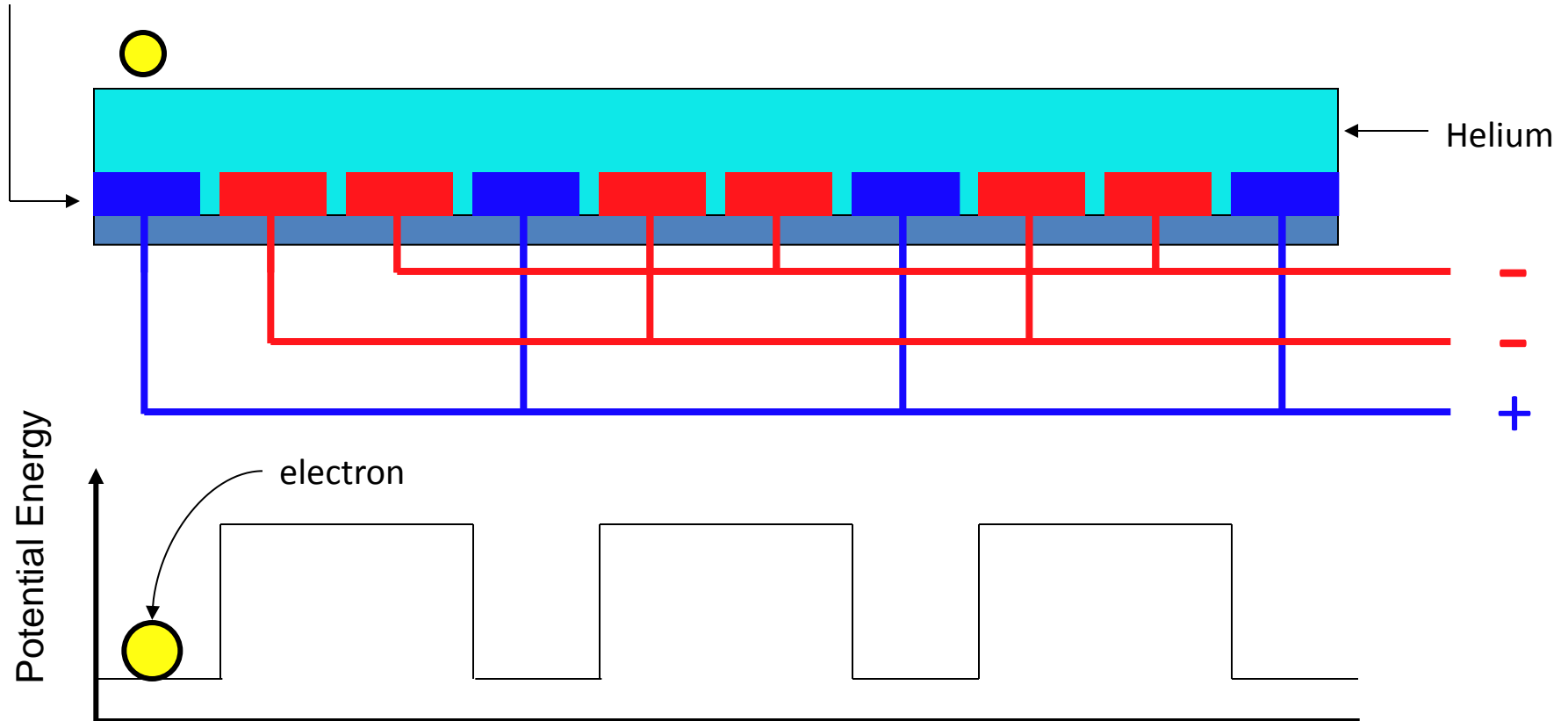
# Sandia Device



# 3-phase CCD

## Potential

Underlying gates

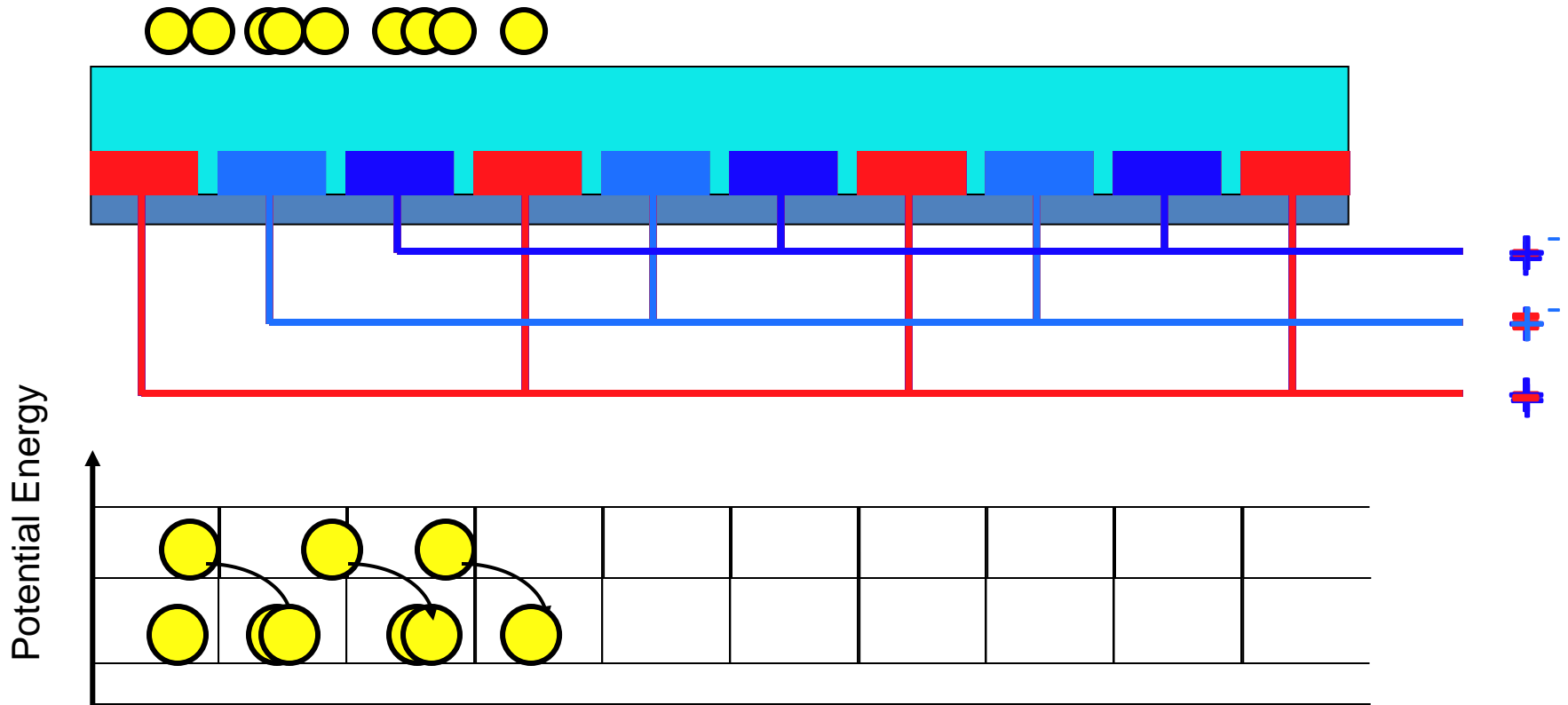


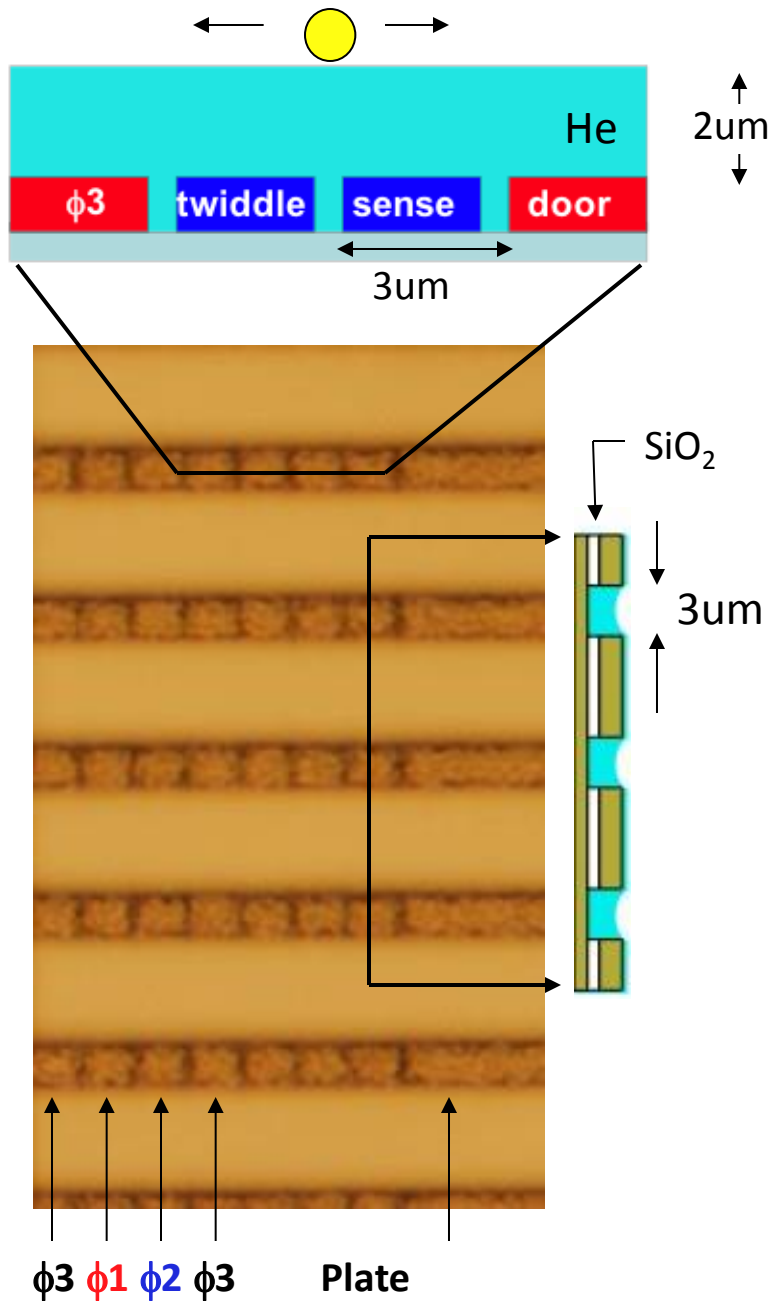


# 3-phase CCD

Clocking  $\Phi$

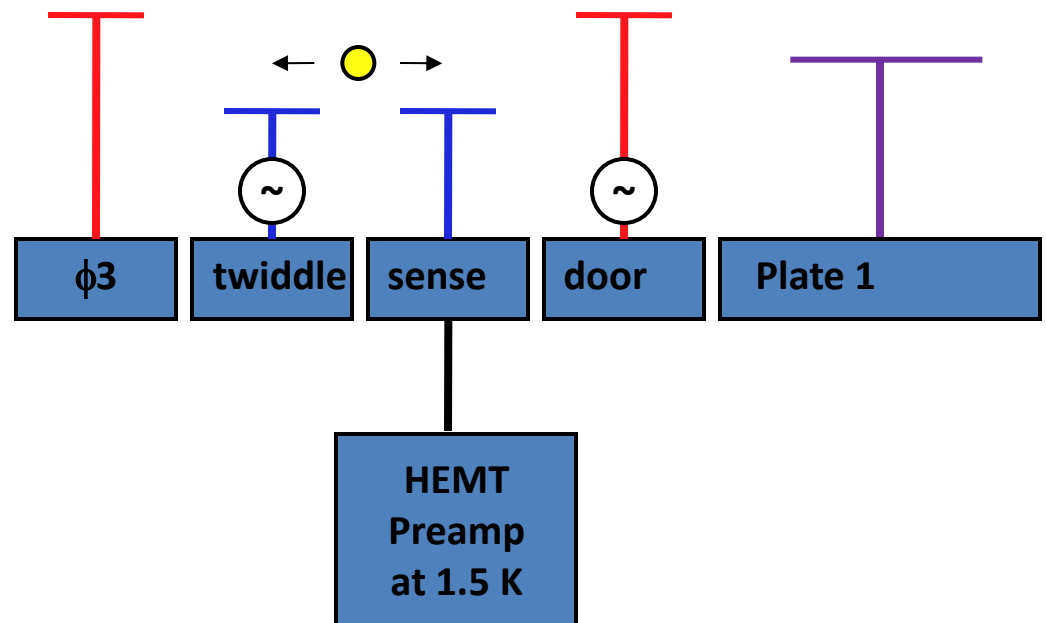
Electron has moved one pixel (3 gates) to the right





## Measurement

Modulate twiddle to push  
 electron on and off the sense gate



# Horizontal CCD

## Loading:

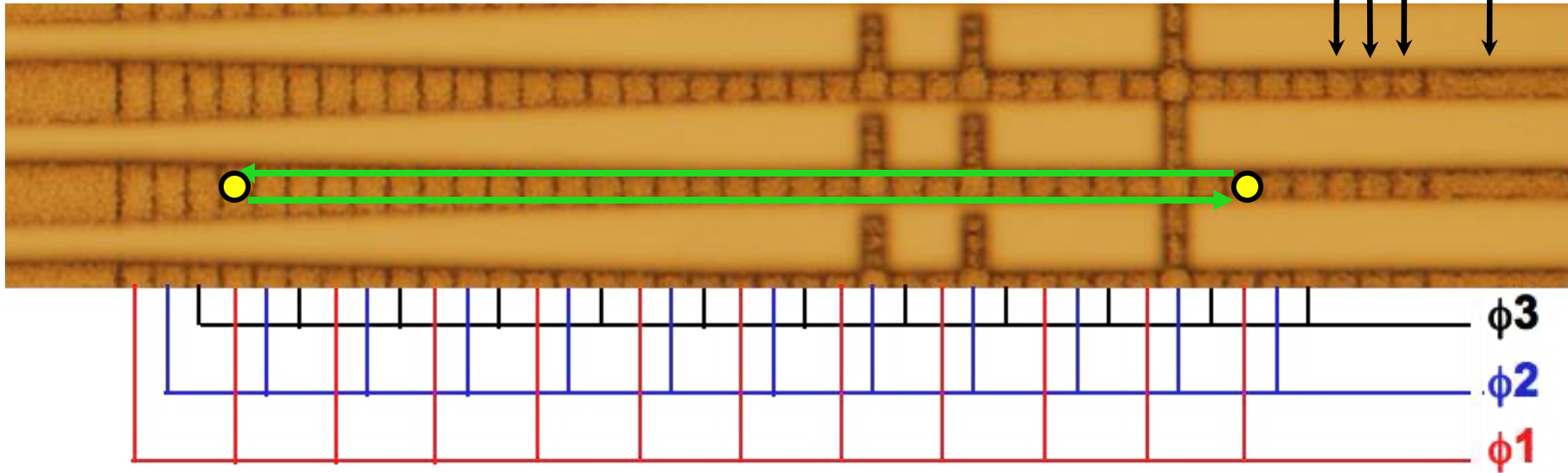
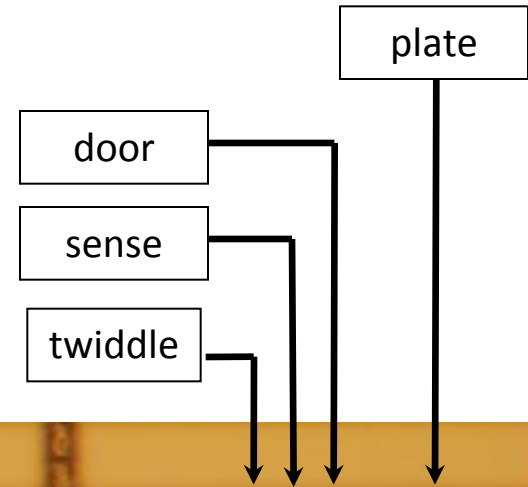
Photoemit electrons on plates

Load them to pixels by opening the door

## Clocking Sequence

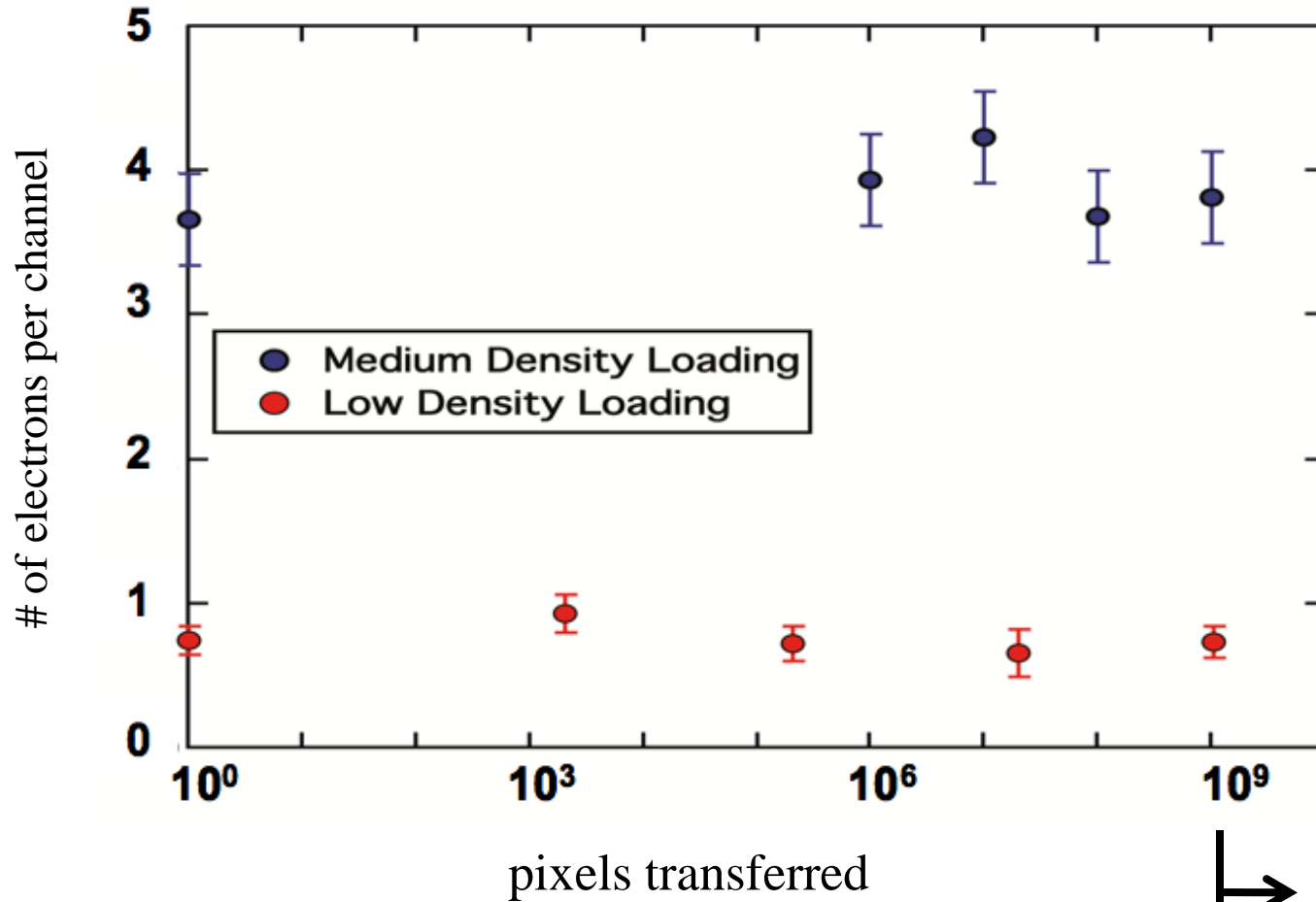
10 pixel to the left

10 pixel back to the right



# Horizontal Clocking Efficiency

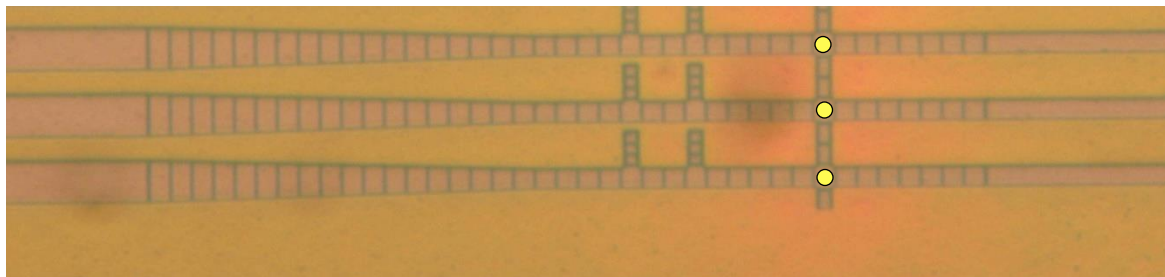
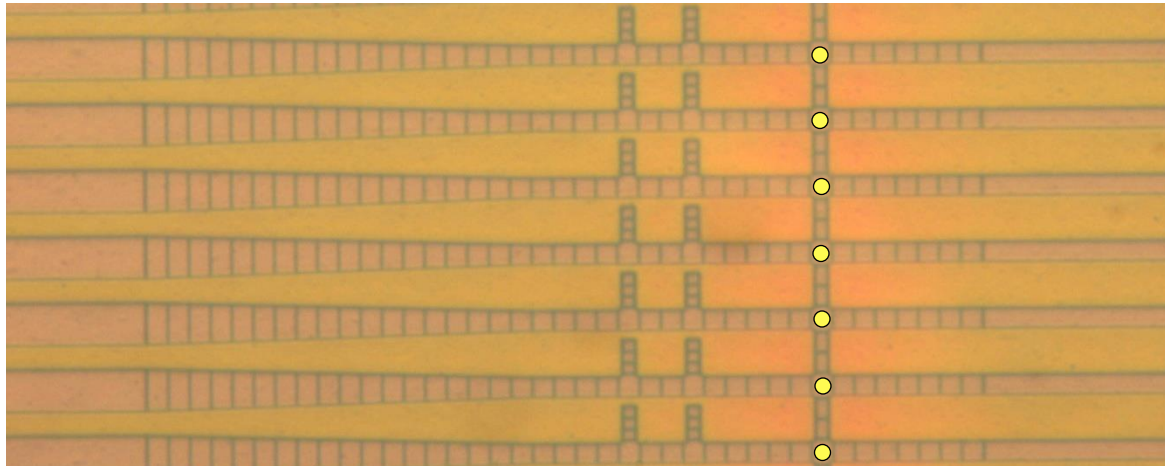
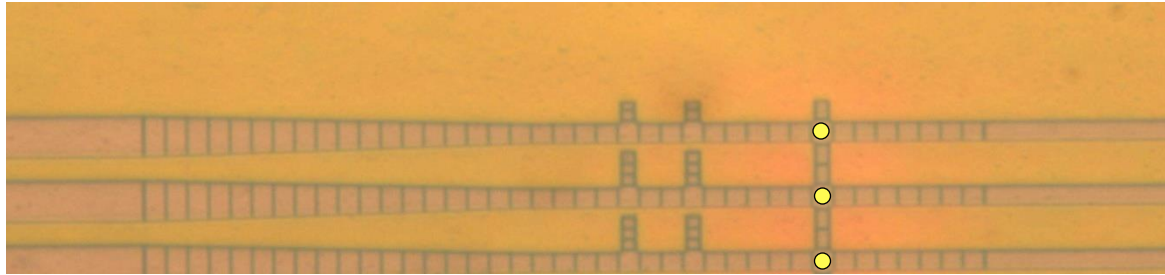
Clock (pixel) rate = 240kHz



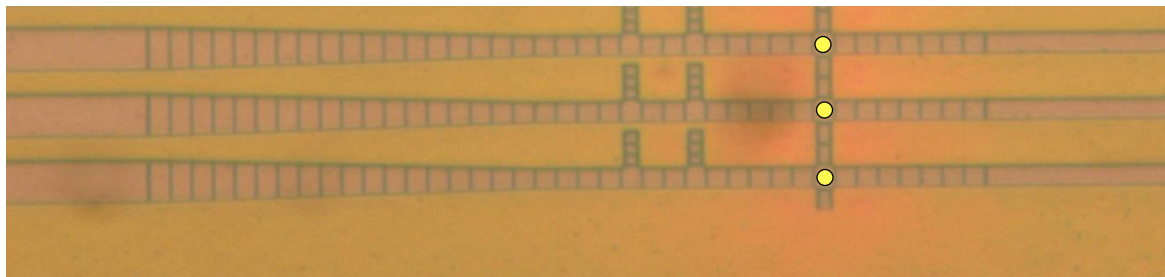
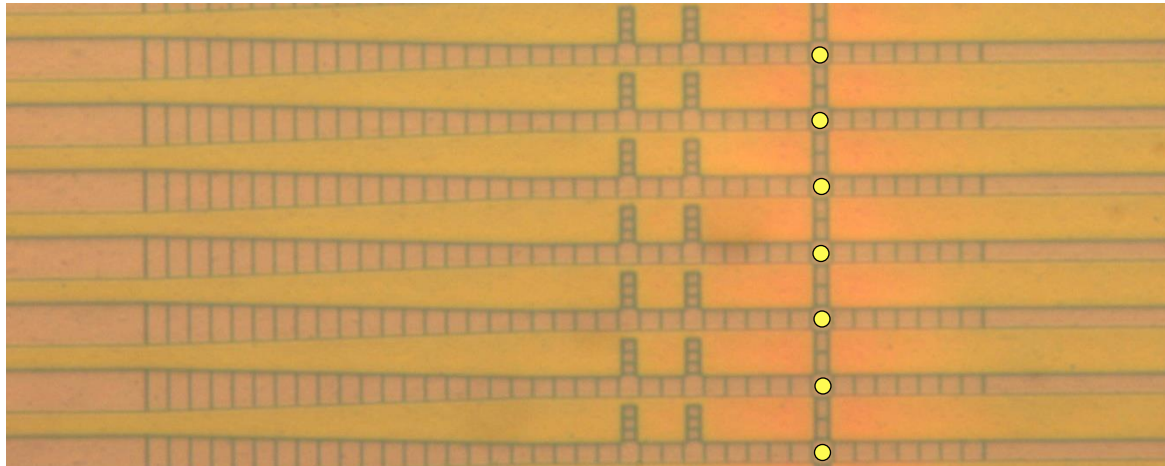
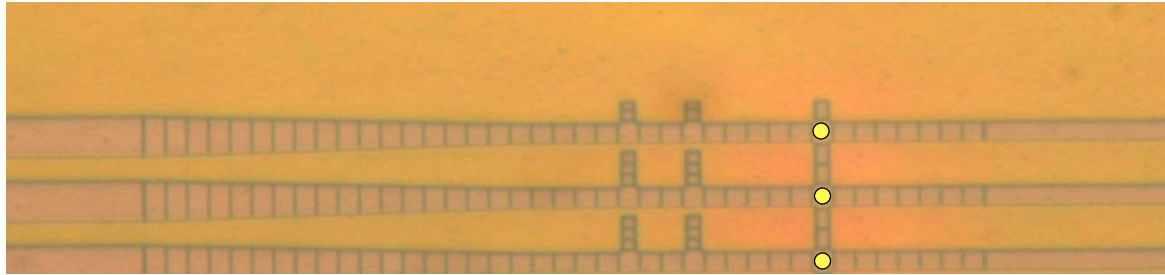
**No measurable errors**

→ ~ 70 min.  
→ ~ 9 km.

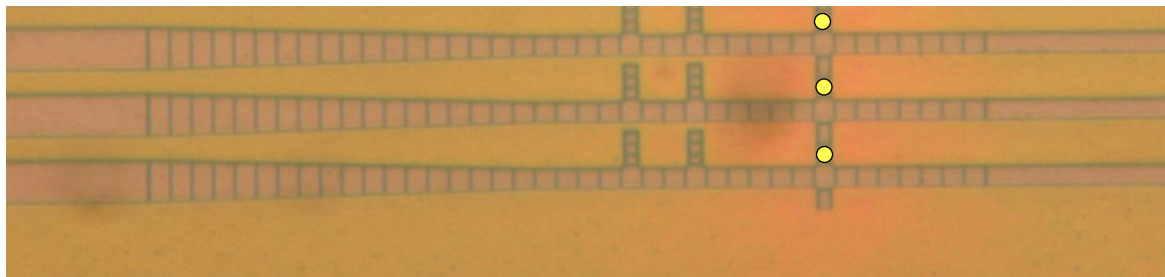
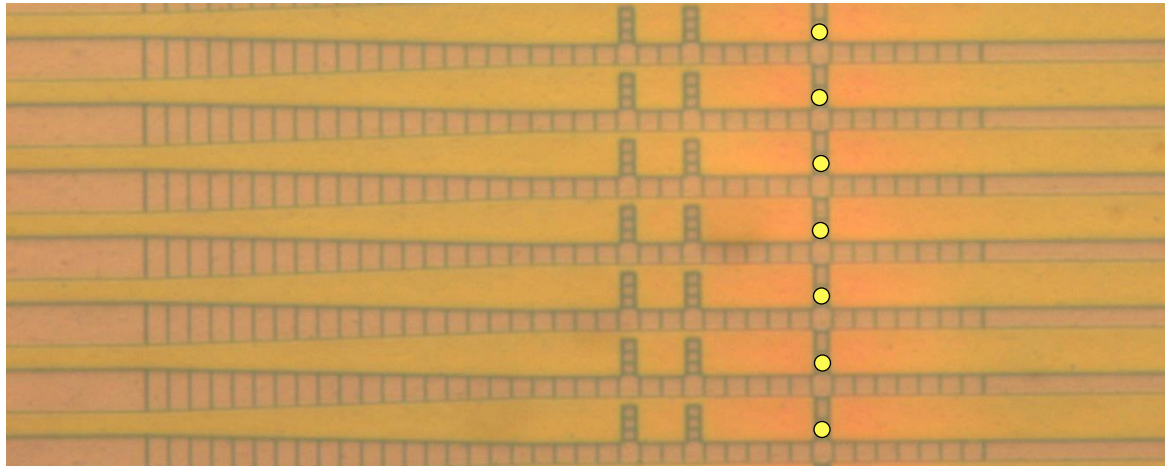
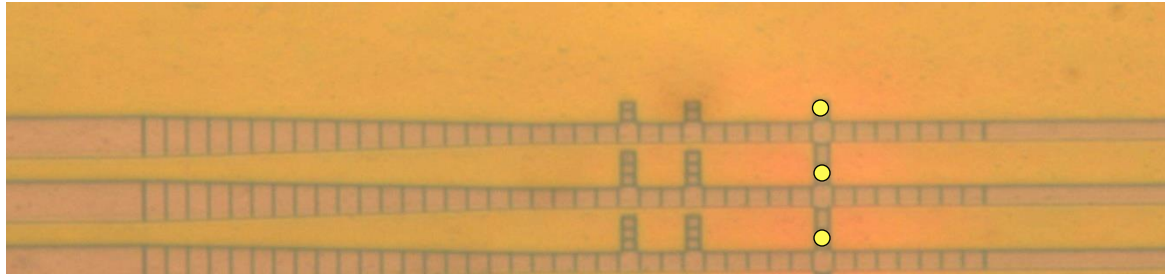
# Vertical Clocking



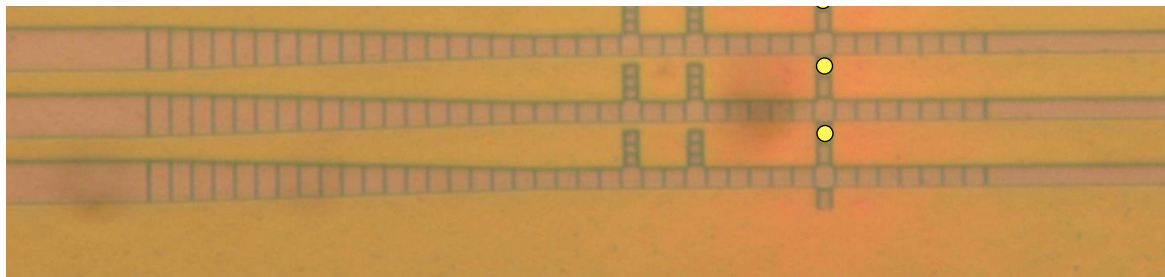
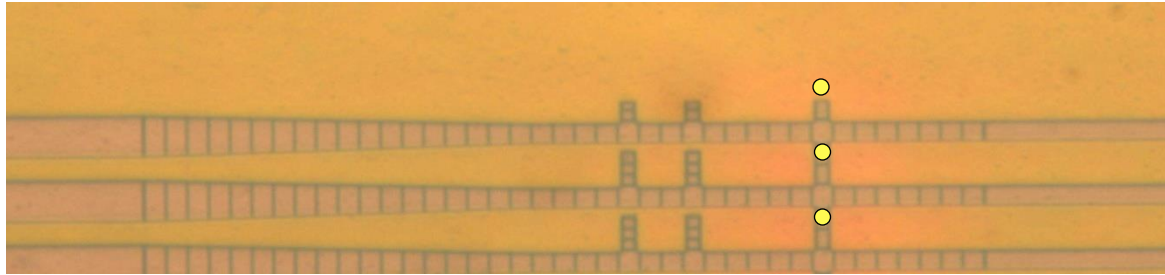
# Vertical Clocking



# Vertical Clocking

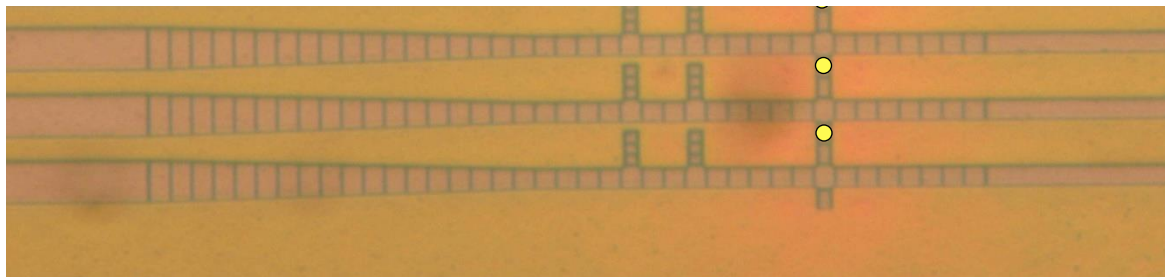
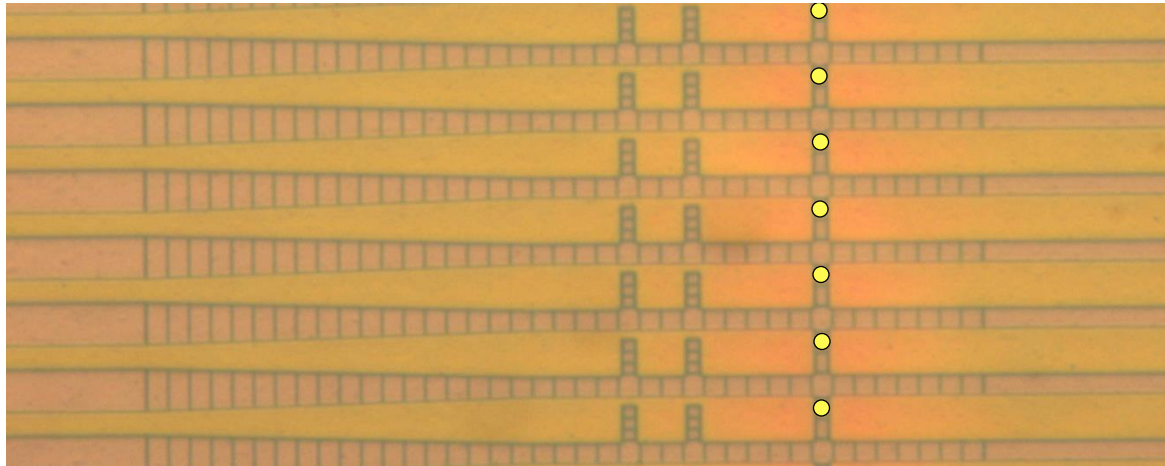
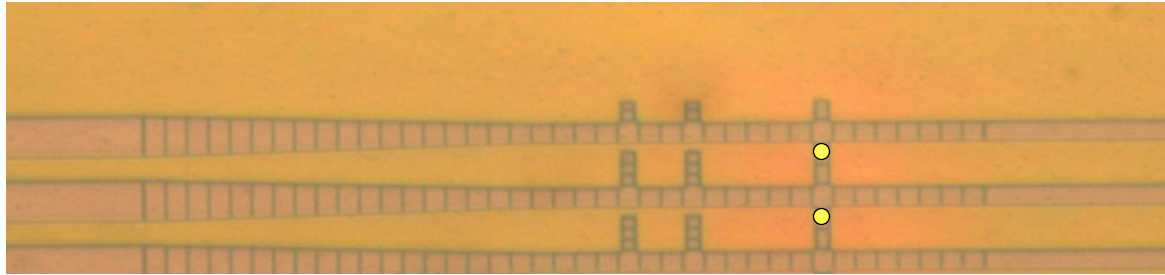


# Vertical Clocking

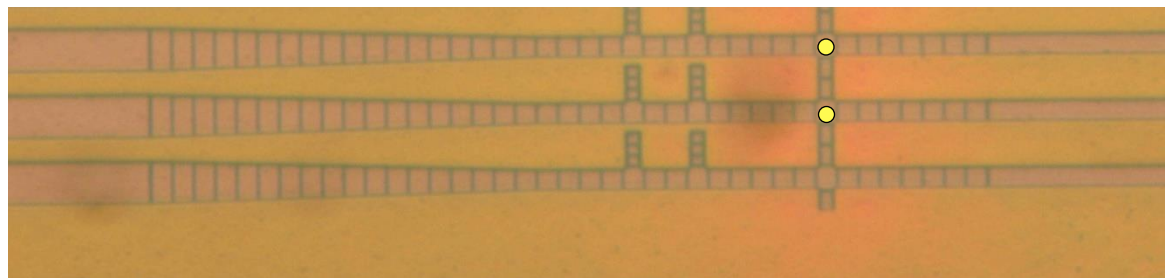
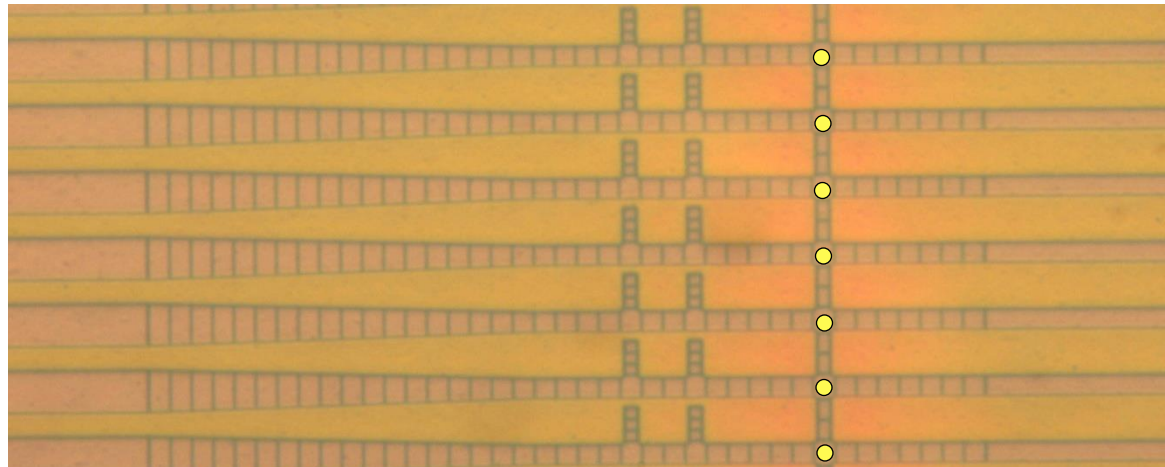
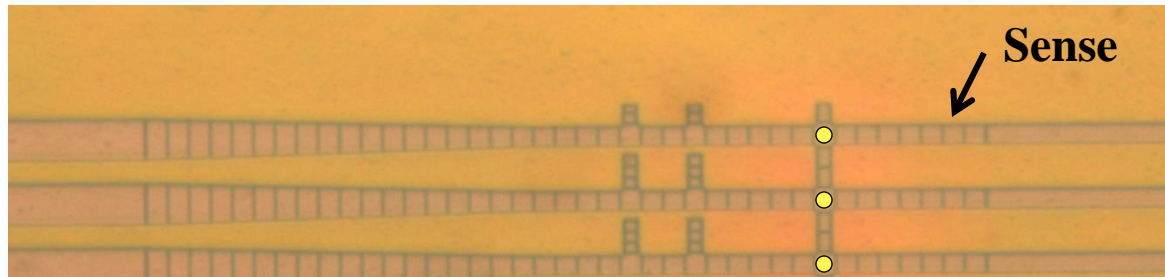




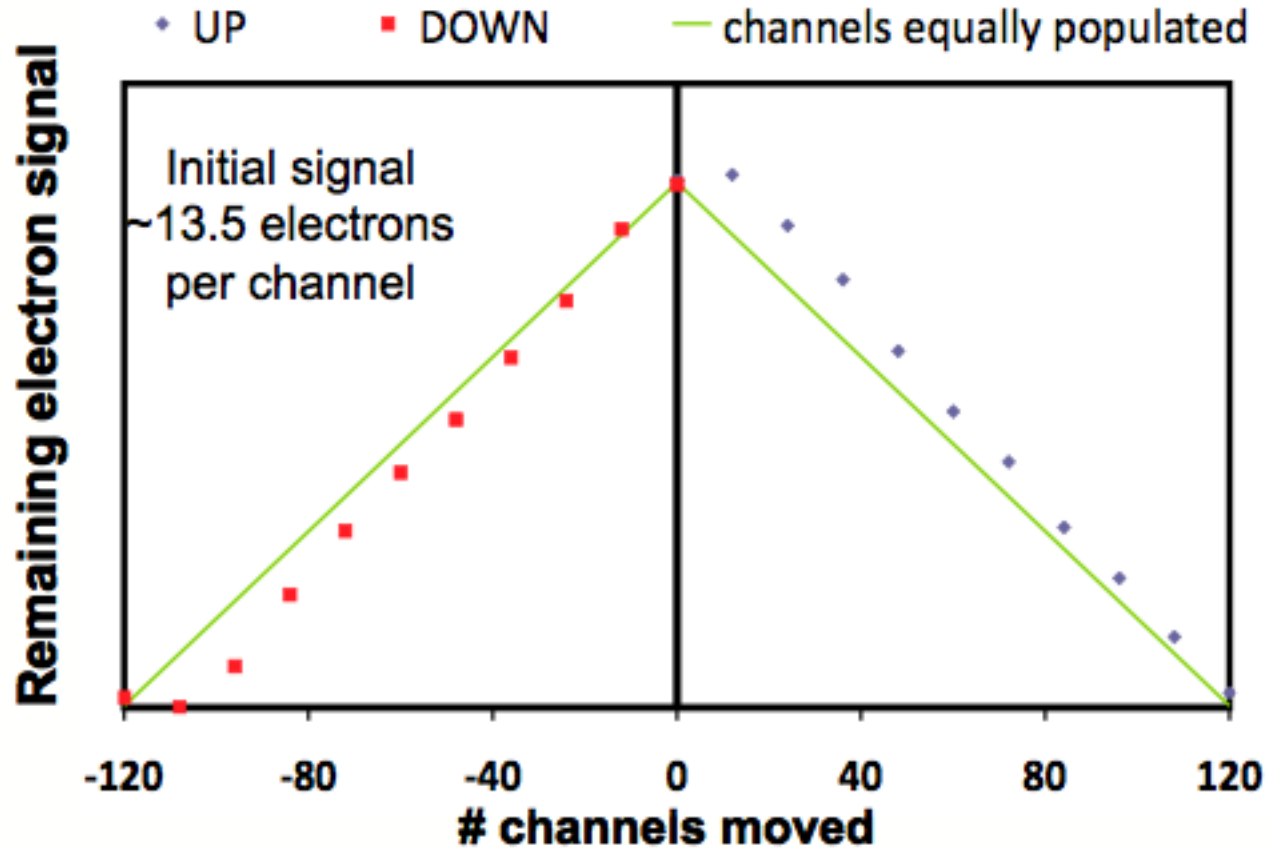
# Vertical Clocking



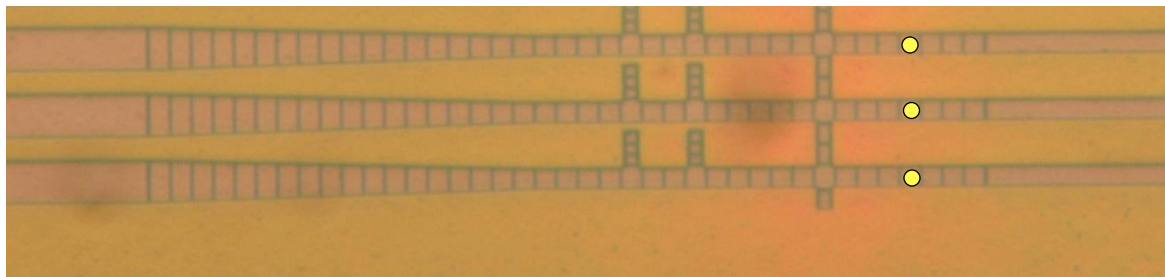
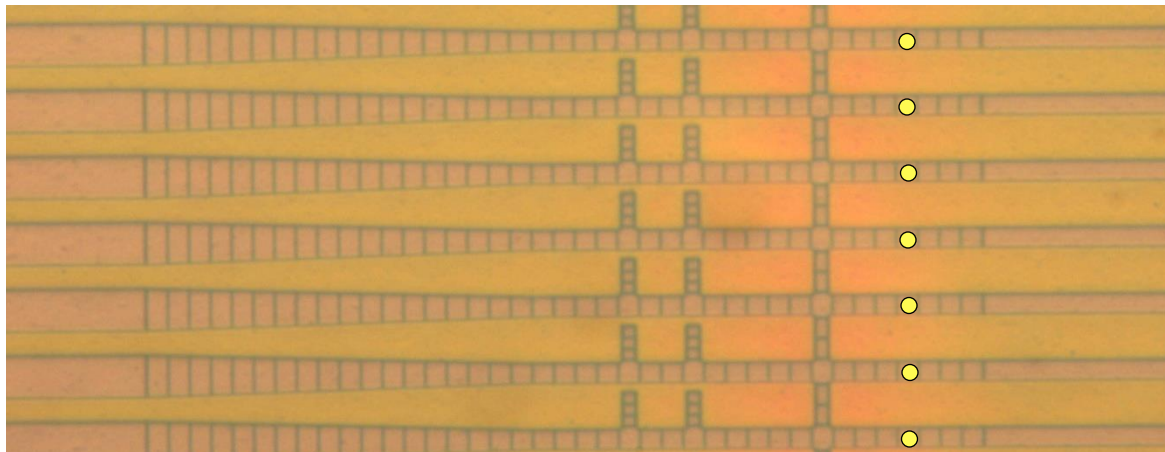
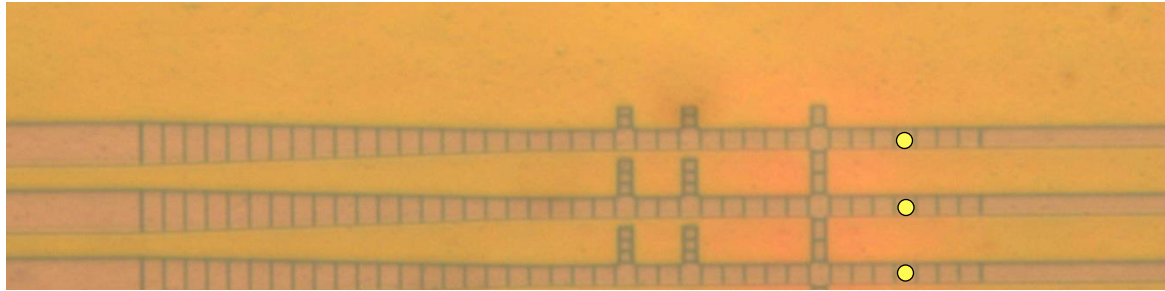
# Vertical Clocking



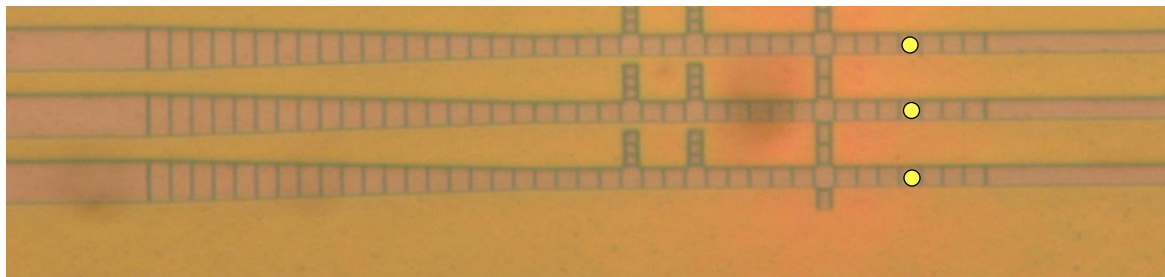
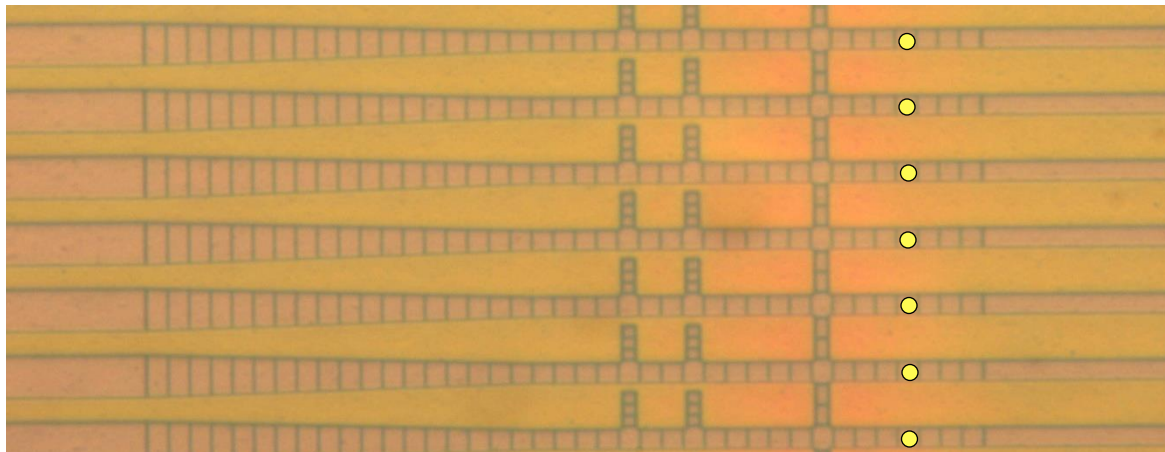
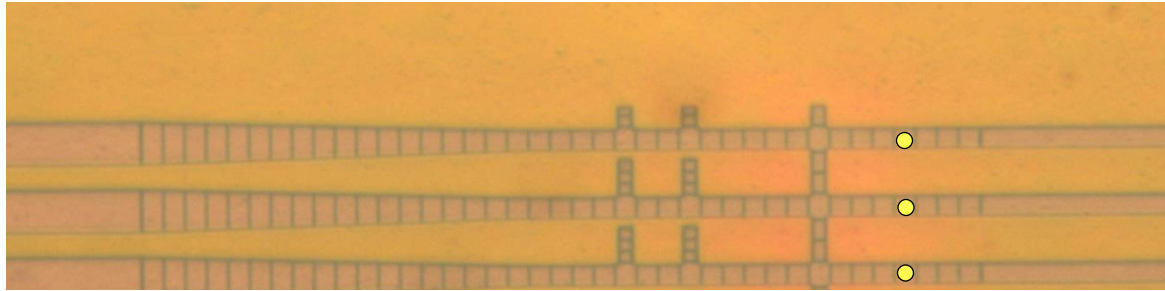
# Channel Occupancy



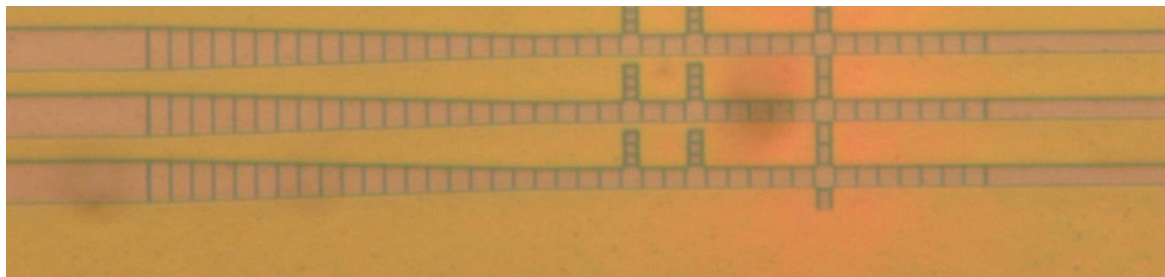
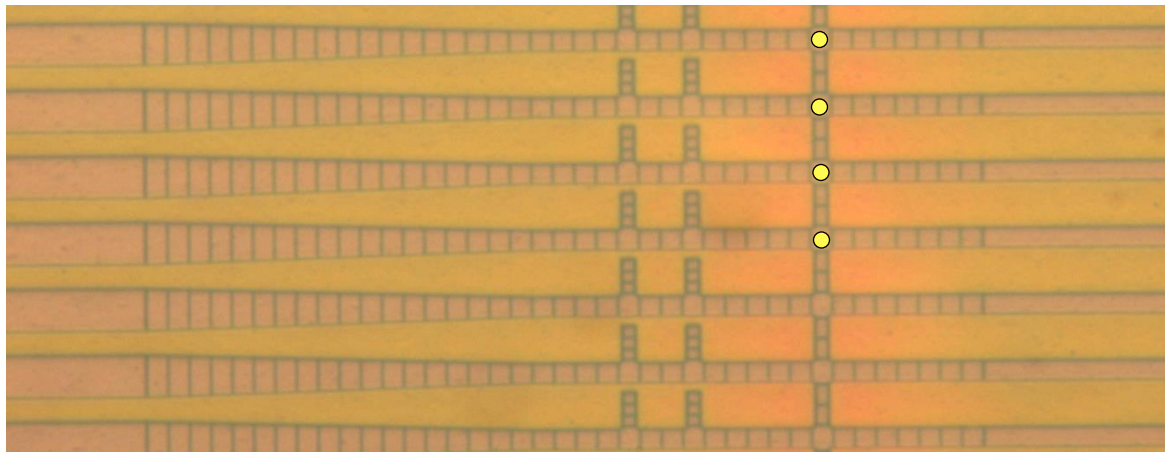
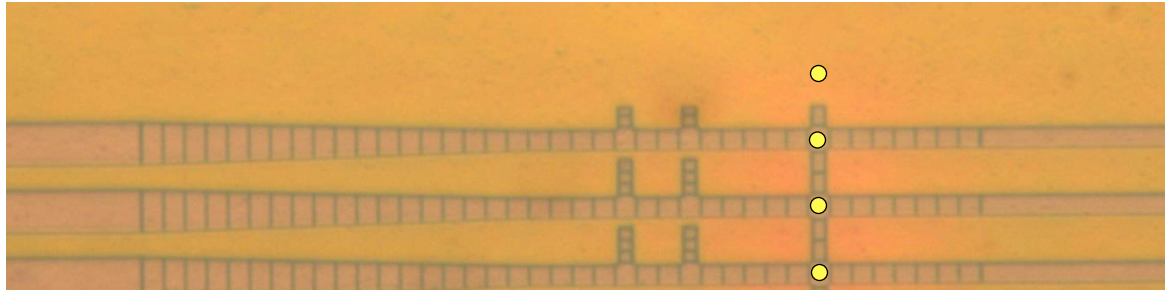
# Vertical Clocking



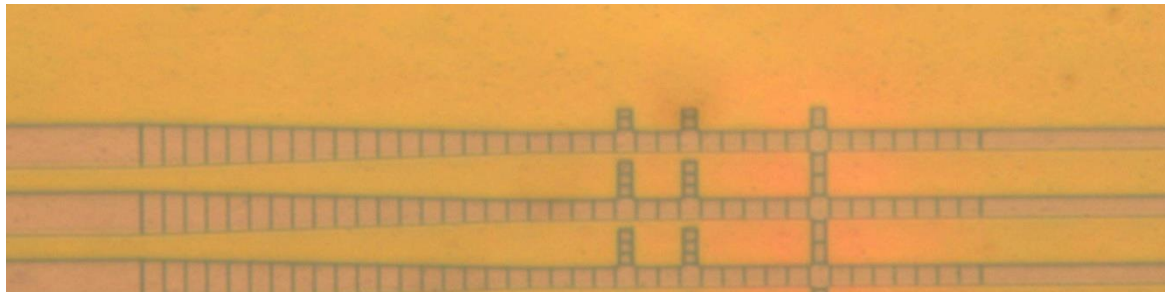
# Vertical Clocking



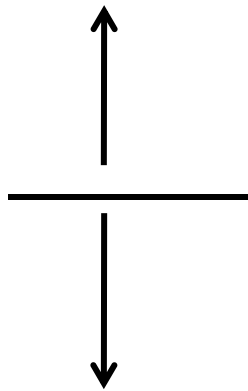
# Vertical Clocking



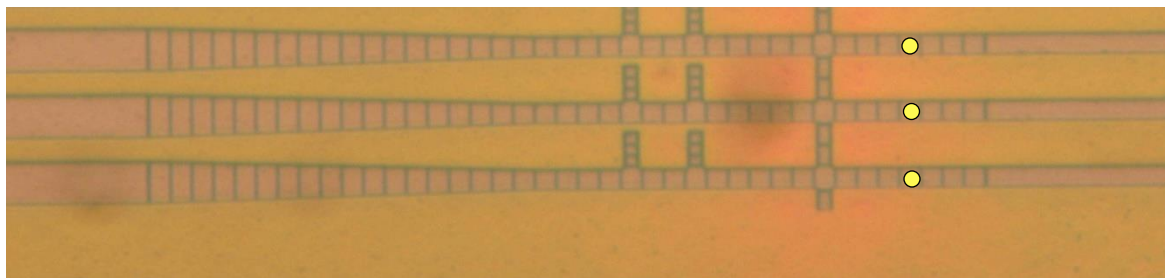
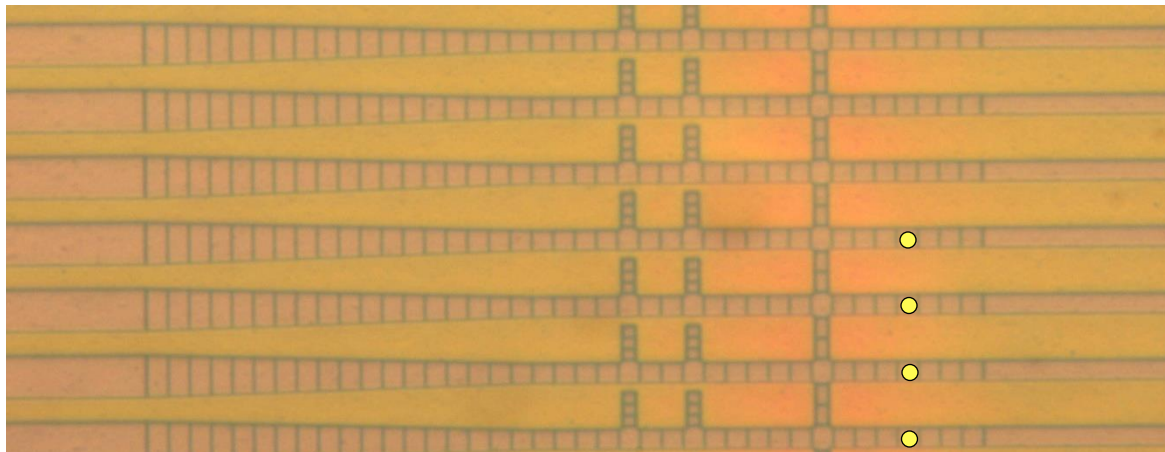
# Vertical Clocking



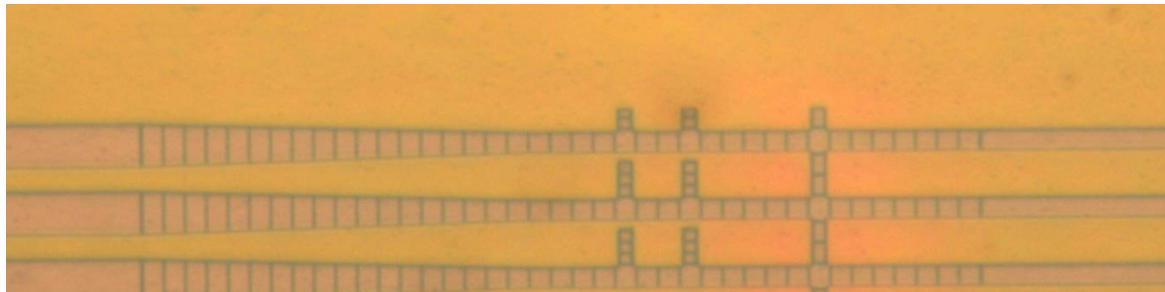
60 Channels



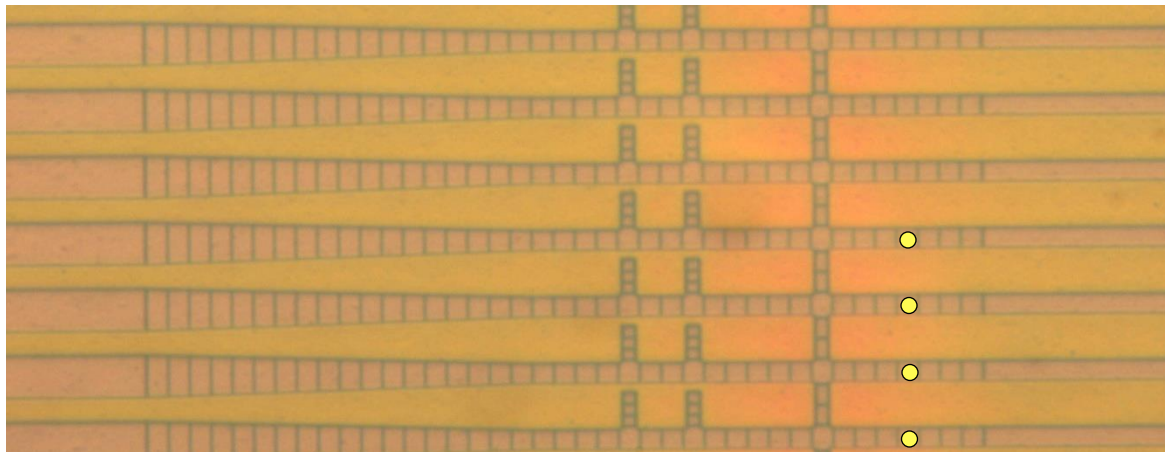
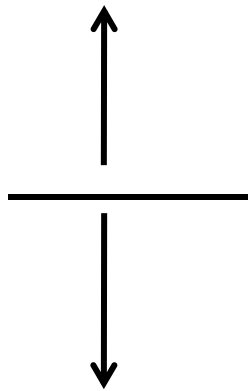
60 Channels



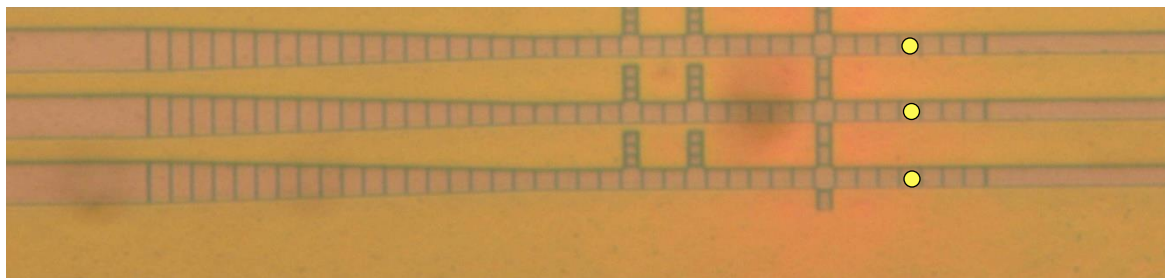
# Vertical Clocking



60 Channels

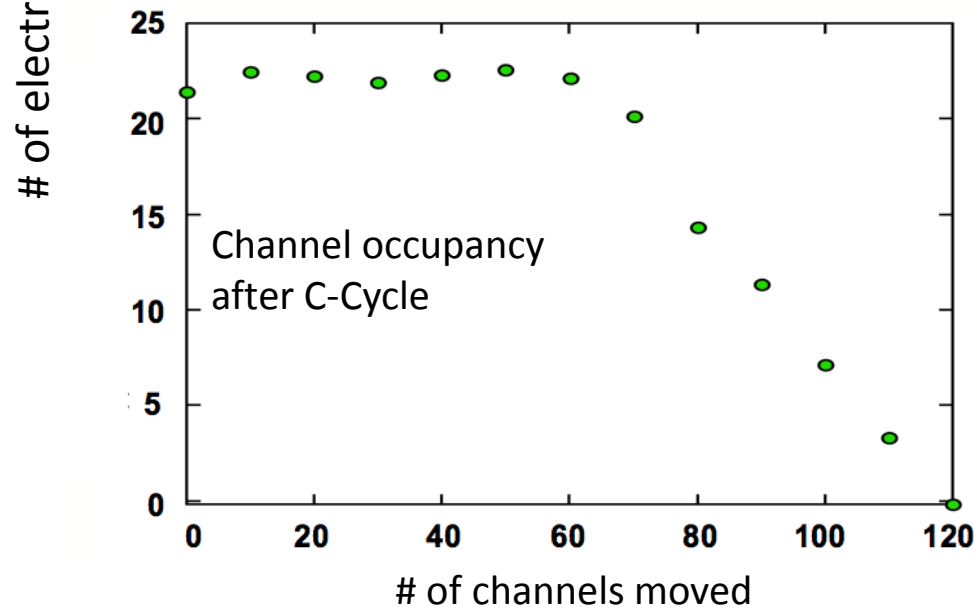
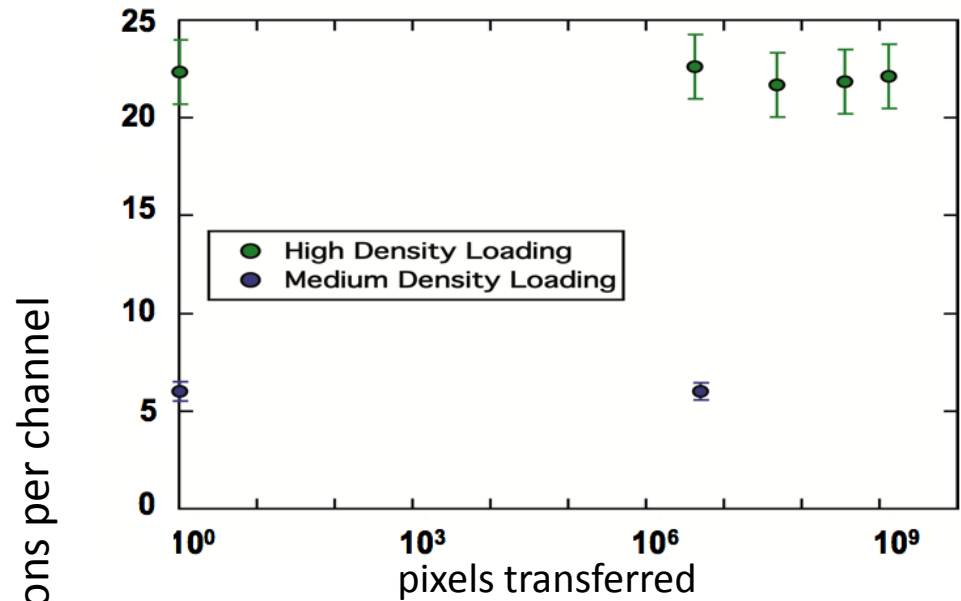


60 Channels





# Vertical (“C-cycle”) Efficiency

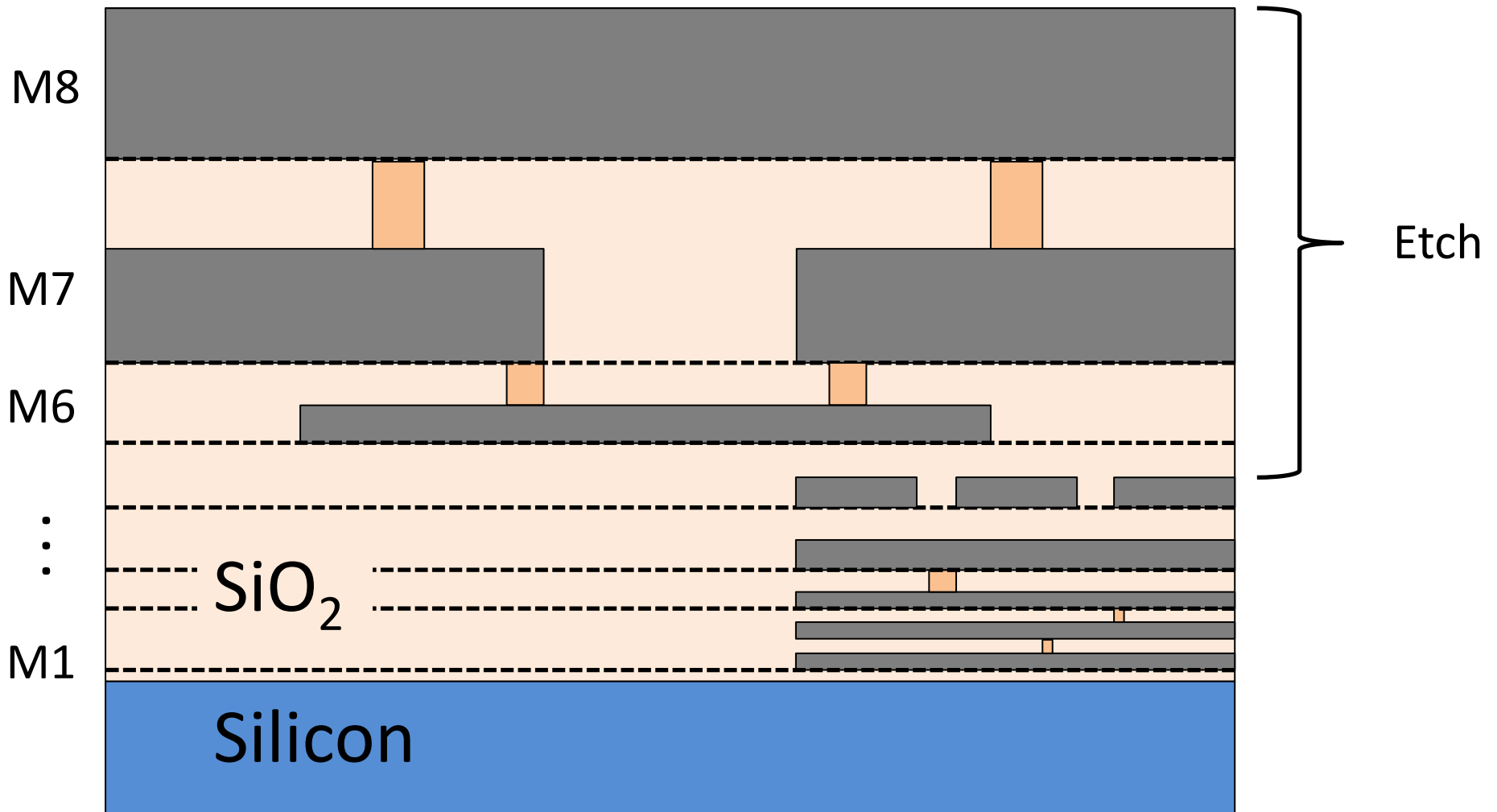


## Conclusions for electrons on superfluid helium channels with silicon integrated circuits (Sandia device)

- Unprecedented reliability of a Charge Coupled Device
  - Essentially a perfect Electron Transfer Efficiency
- 5 clock lines for full control
  - 2D Scalability: Move anywhere in our ~5000 position gate & channel array
- Si-Processing
  - First, non-optimized design with standard silicon processing
  - Possibilities for on-chip amplification
  - On-chip multiplexer
  - More...

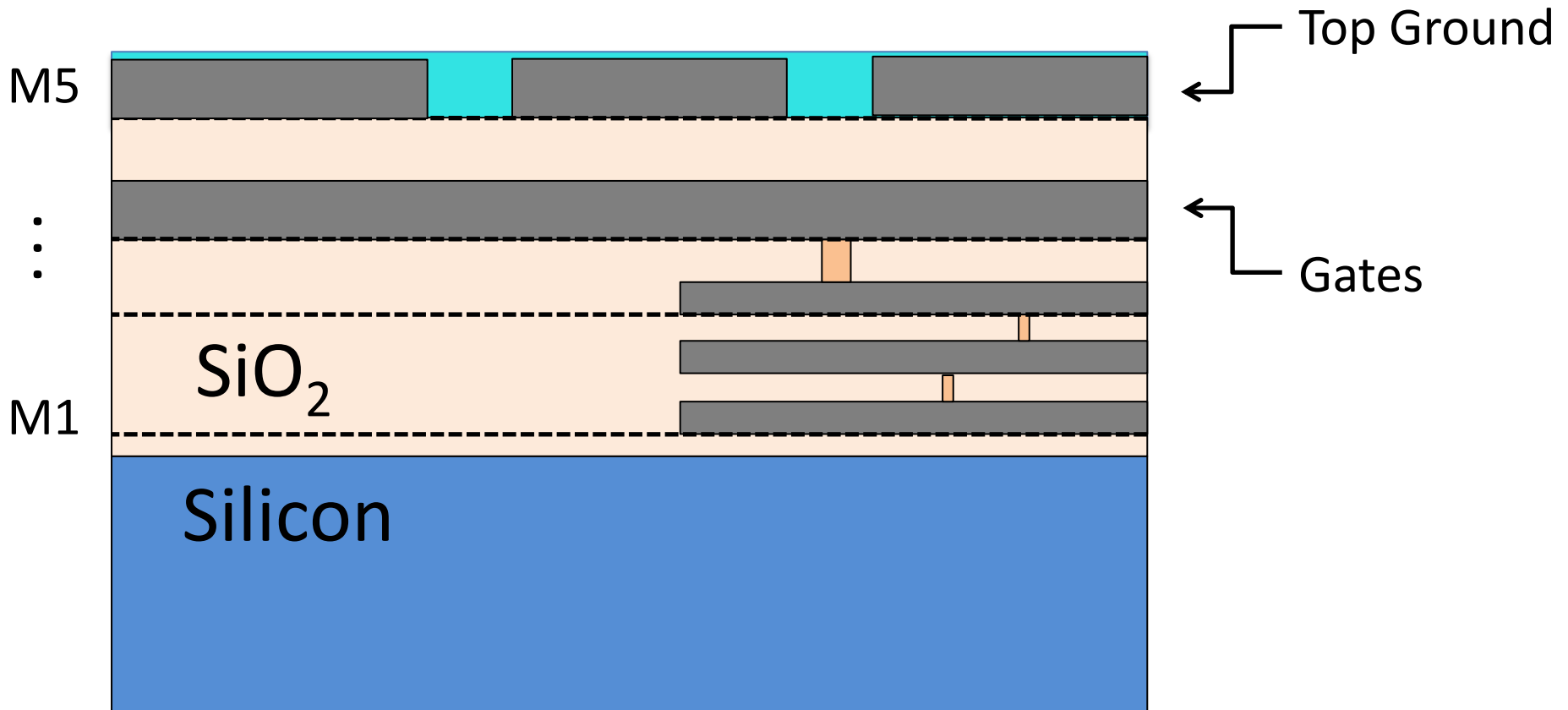
# IBM CMOS

8 metal layers (Aluminum and Copper)

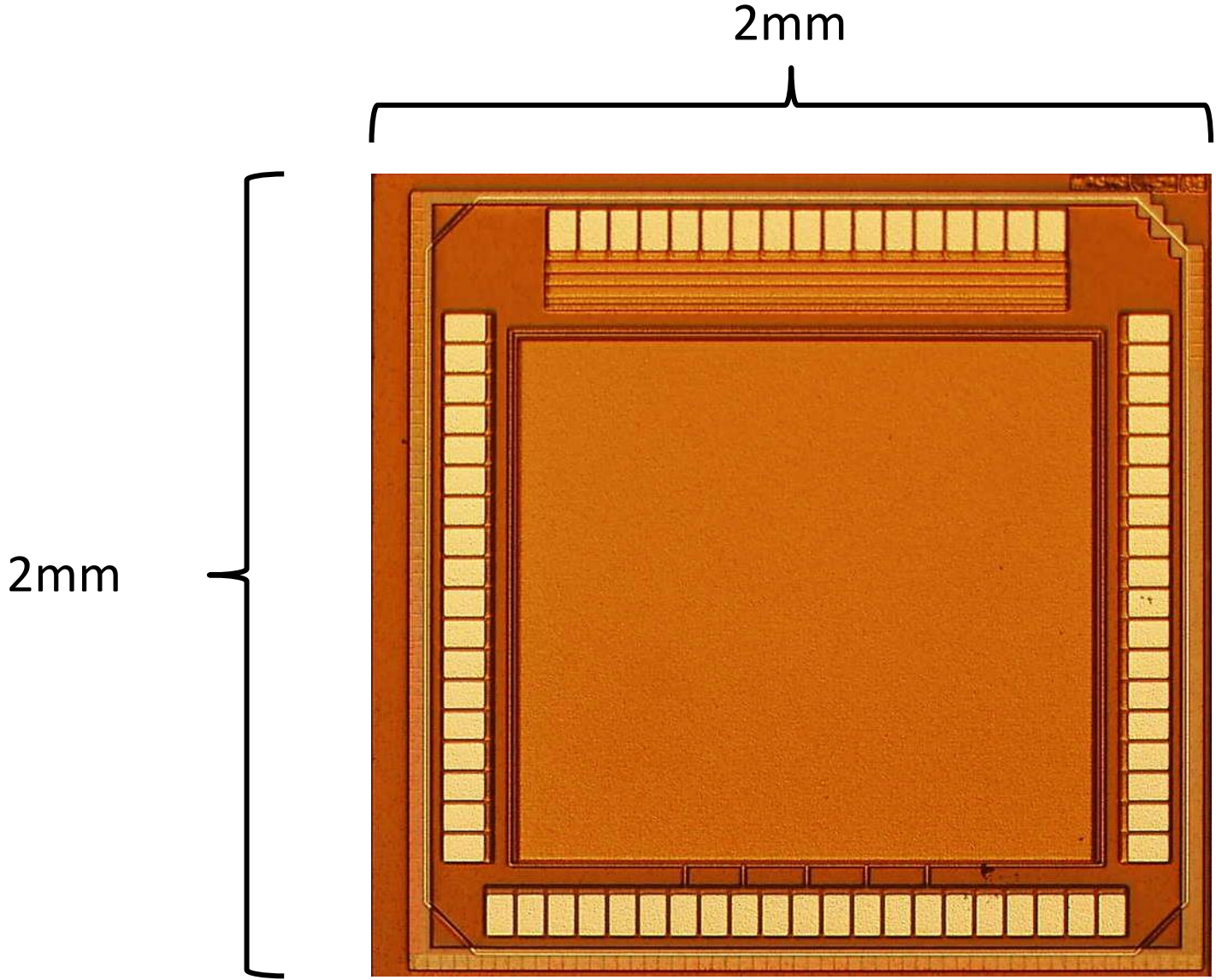


# IBM CMOS

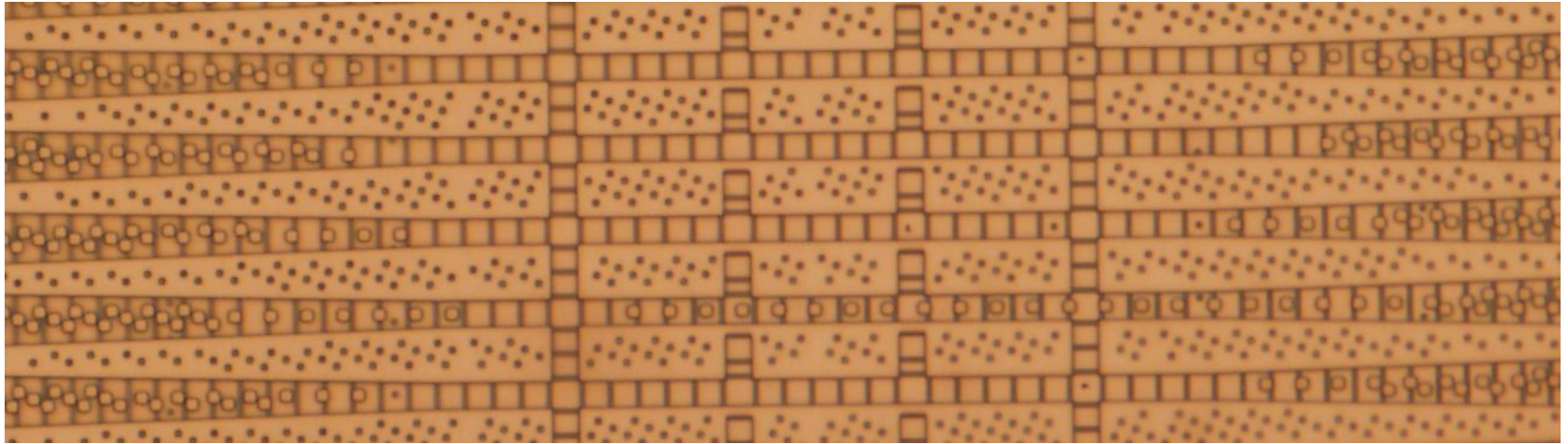
Channels using thin metals



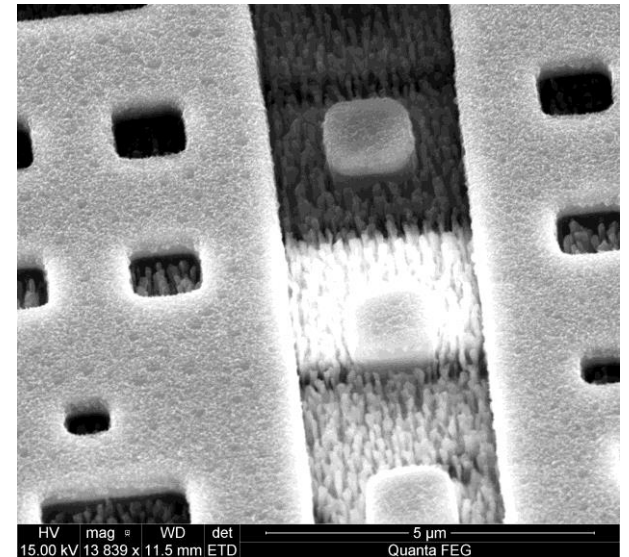
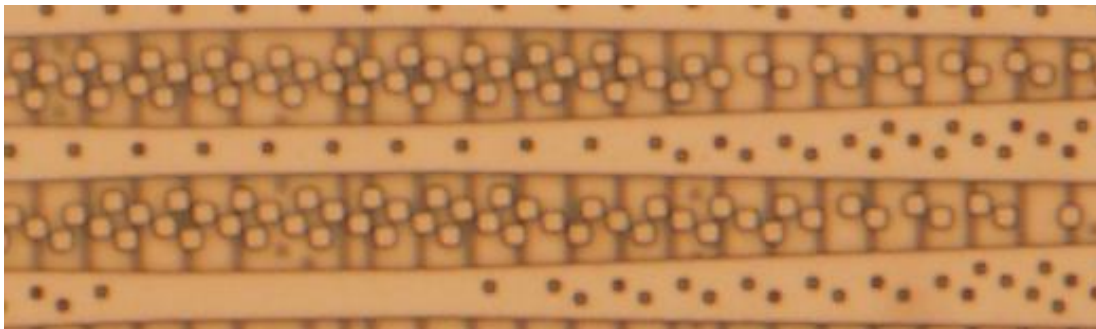
# IBM CMOS



# IBM CMOS



Filling and cheesing!!!!

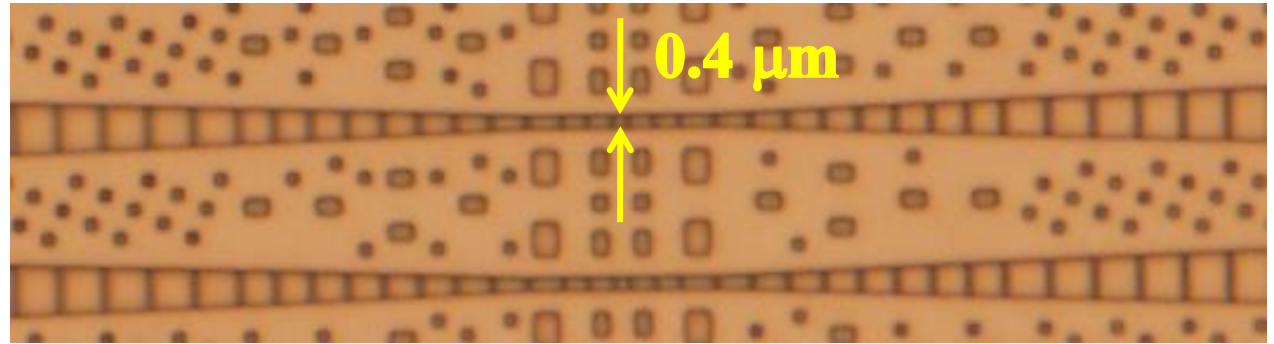


Electroplating? Electro chemistry?

# IBM CMOS

## Turnstile

Single Electron loading



ONE AT A TIME!!!

# IBM CMOS

- Turnstile
- Quantum dots



**Need better sensing**

On-chip amplification?  
What else?



# IBM CMOS

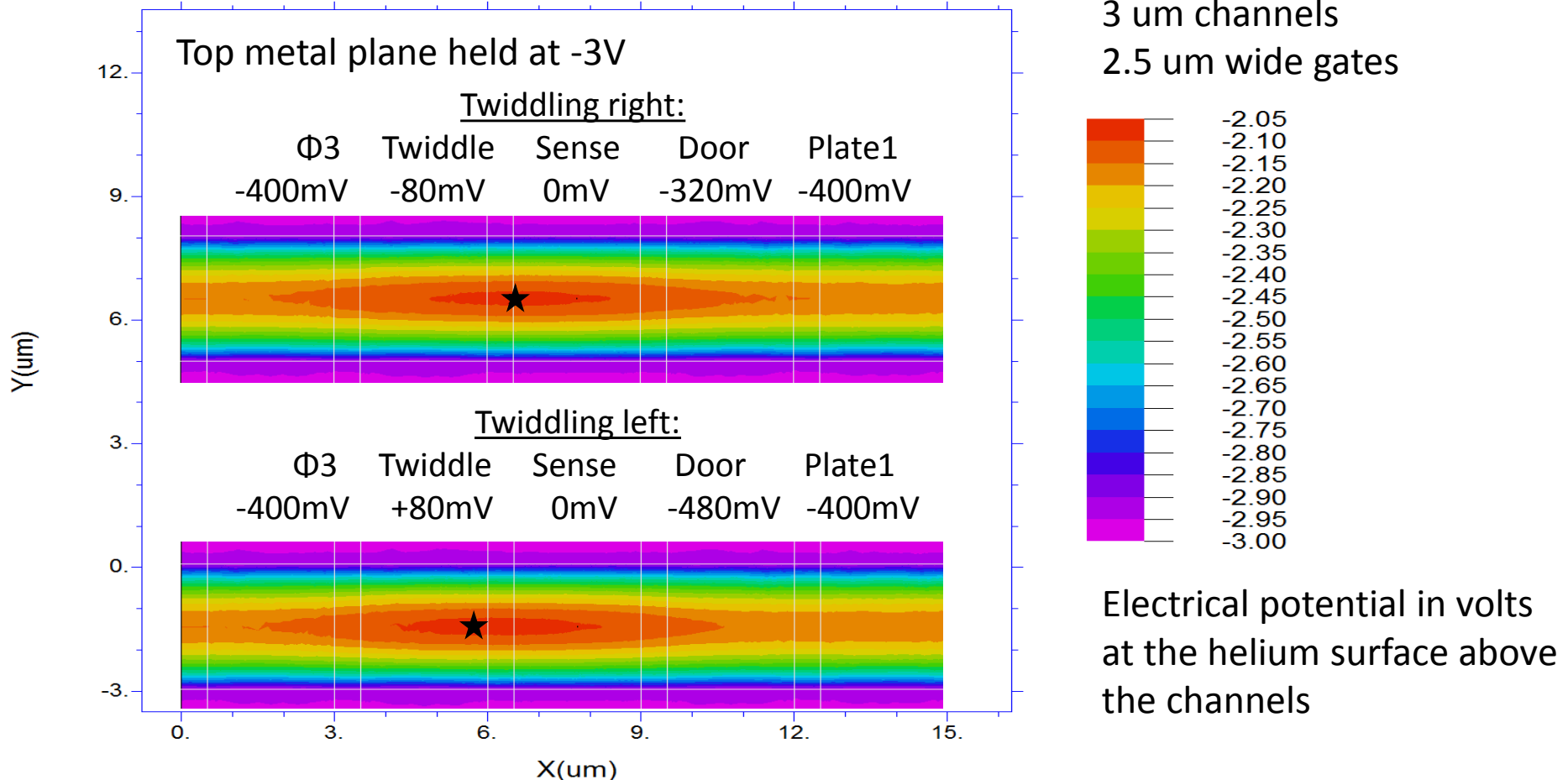
- Turnstile
- Quantum dots



**Need better sensing**

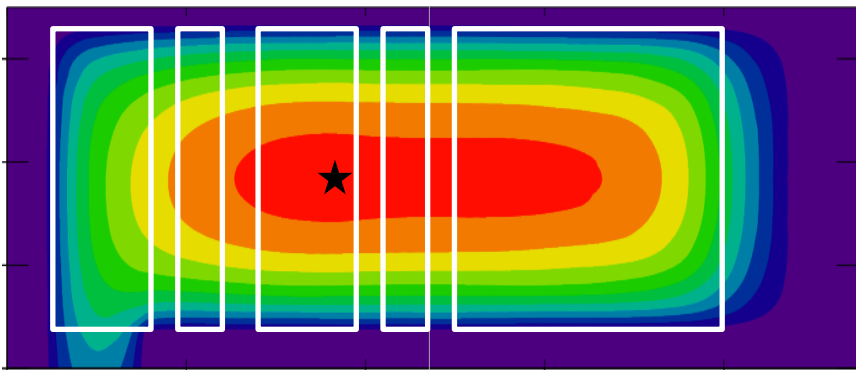
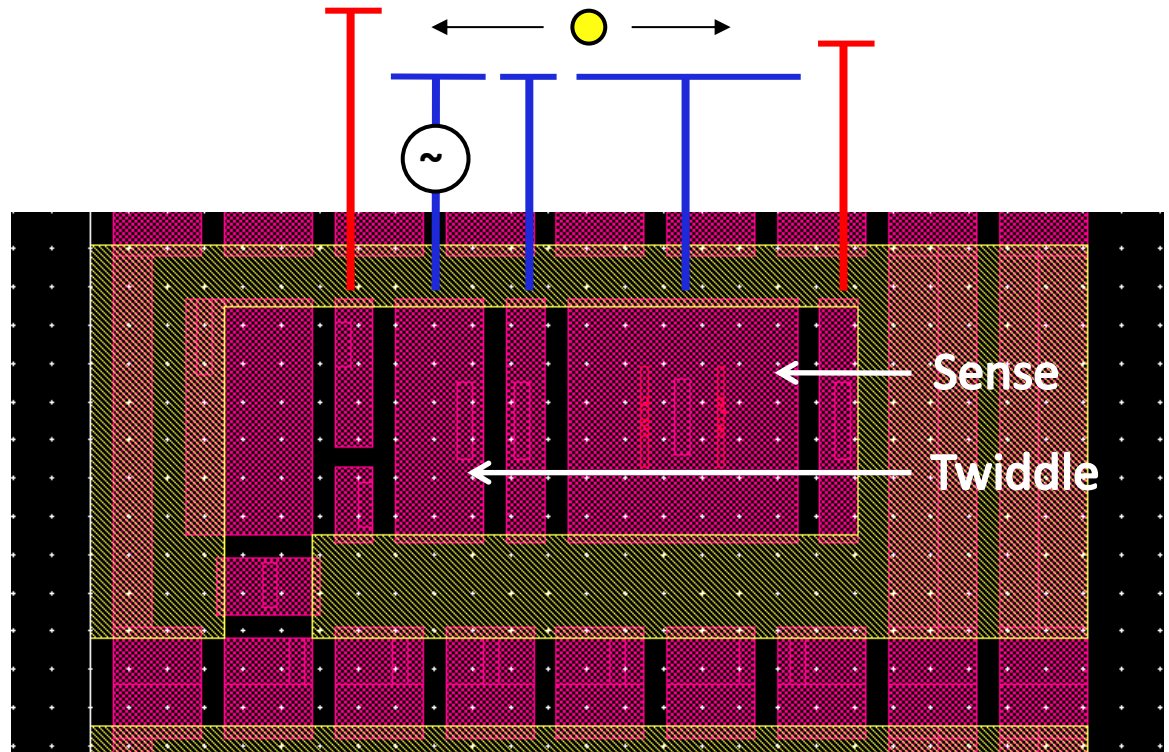
On-chip amplification?  
What else?

## Twiddle Sensor: Potential Simulations

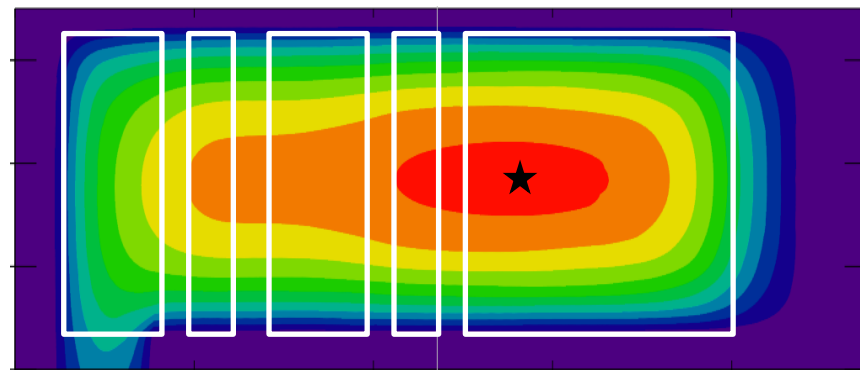


# Wider gates!!!

- 6 X 6 um Sense gate
- Gate in between Sense and Twiddle



Twiddle



Sense

# What do we do for our next chip???

1. Narrower channels (avoid filling)
2. Narrower gates (avoid cheesing)
3. Some wider gates (better sensing)
4. Turnstile
5. Quantum dots
6. On-chip amplifiers

